

Scanning electron micrograph (SEM) of a 3D topological insulator (TI) Josephson junction. The image shows a central, narrow, dark, zig-zagging channel that runs diagonally across the frame. This channel is flanked by two wider, lighter-colored regions, which appear to be the TI layers. The overall structure is a complex, layered device. The background is a dark, textured surface, likely the substrate or the surrounding TI material.

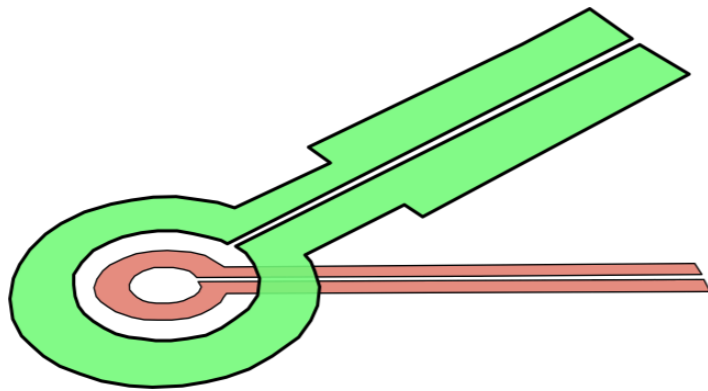
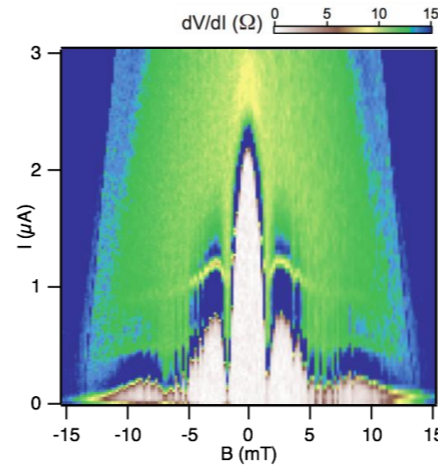
Deconstructing 3D TI Josephson Junctions

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KITP-Majorana Workshop
Dec. 11, 2012

Outline

Motivation and background

Interesting deviations from normal Josephson junction behavior noted in devices made from Bi_2Se_3
Phys. Rev. Lett. **109** 056803 (2012)



Scanning SQUID measurements of JJ Rings

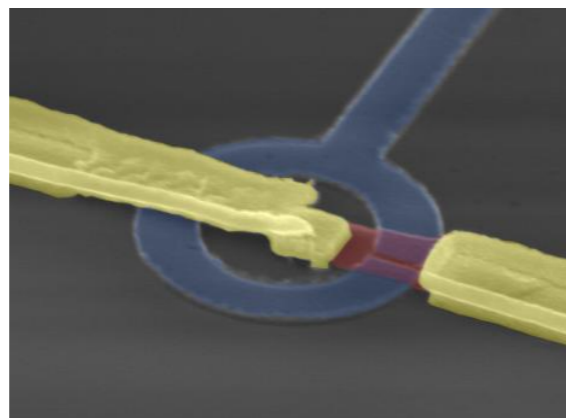
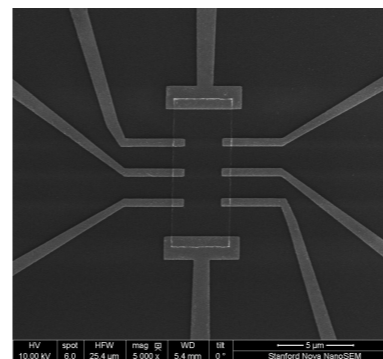
Devices

Curious features in the data

Must closely examine the S-TI interface

Highly Tunable TI films grown by MBE

Devices created from thin MBE TI can be routinely tuned through the “Dirac” point



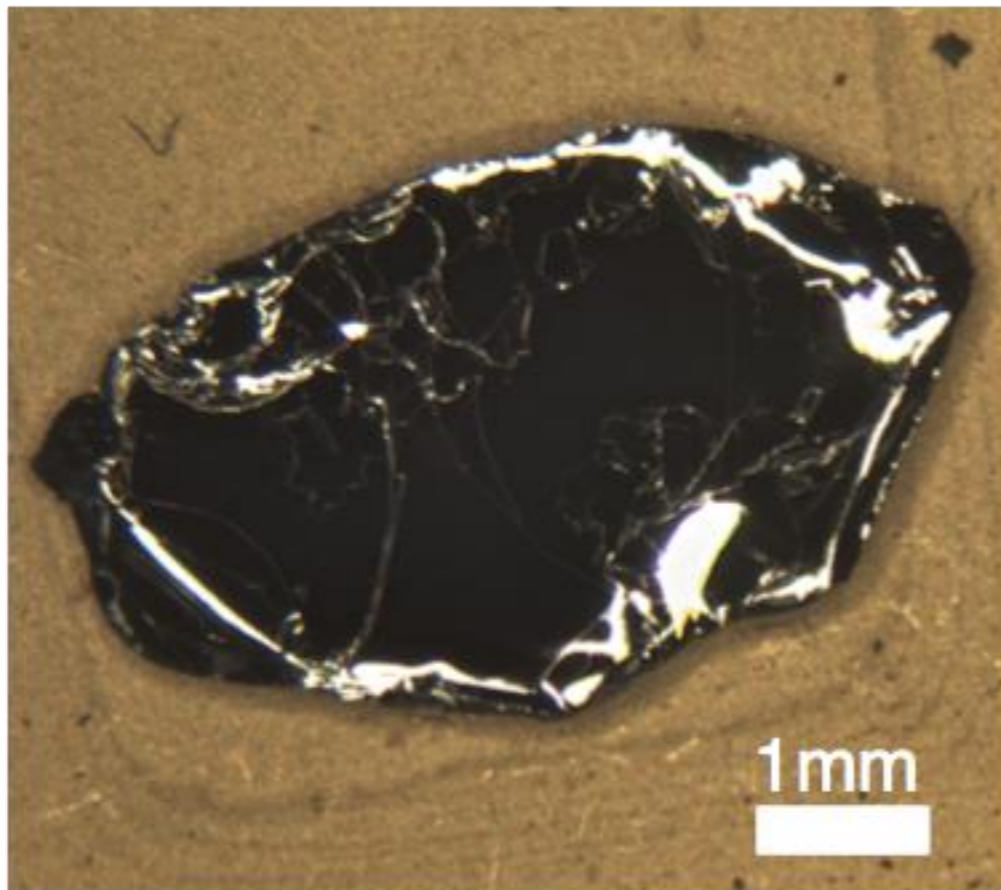
New Measurements

Work by Wieder et al. caused us to look at transport along junction

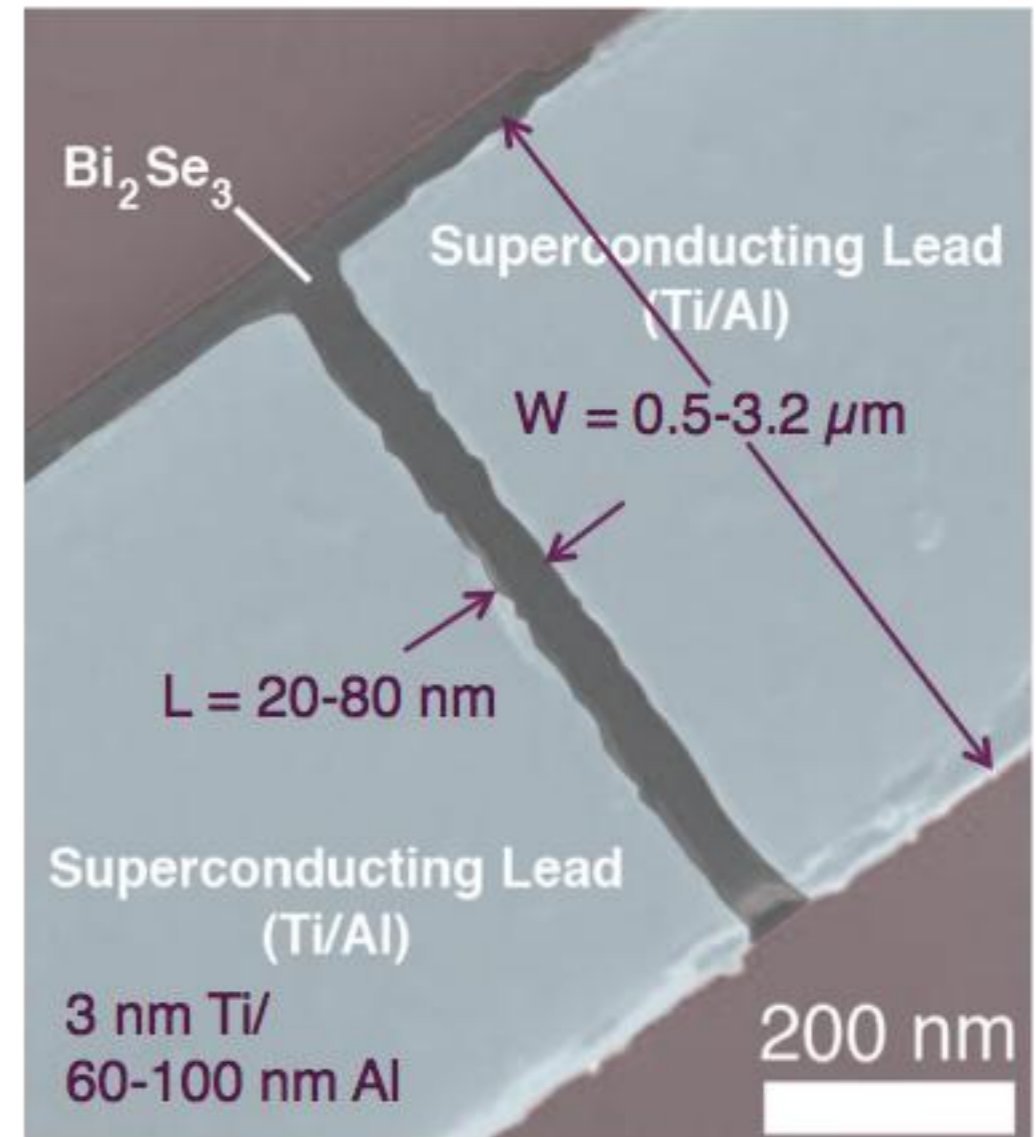
Unexpected temperature and bias-dependence seen

Device fabrication

- Mechanical exfoliation, e-beam lithography.

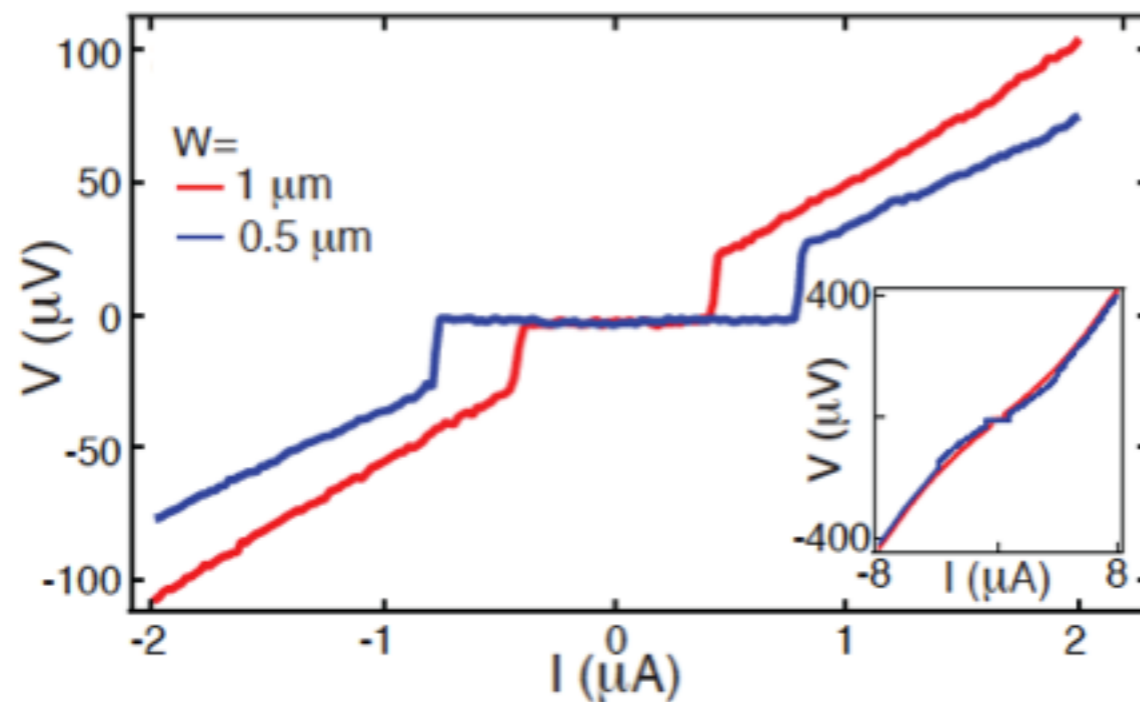


Exfoliation

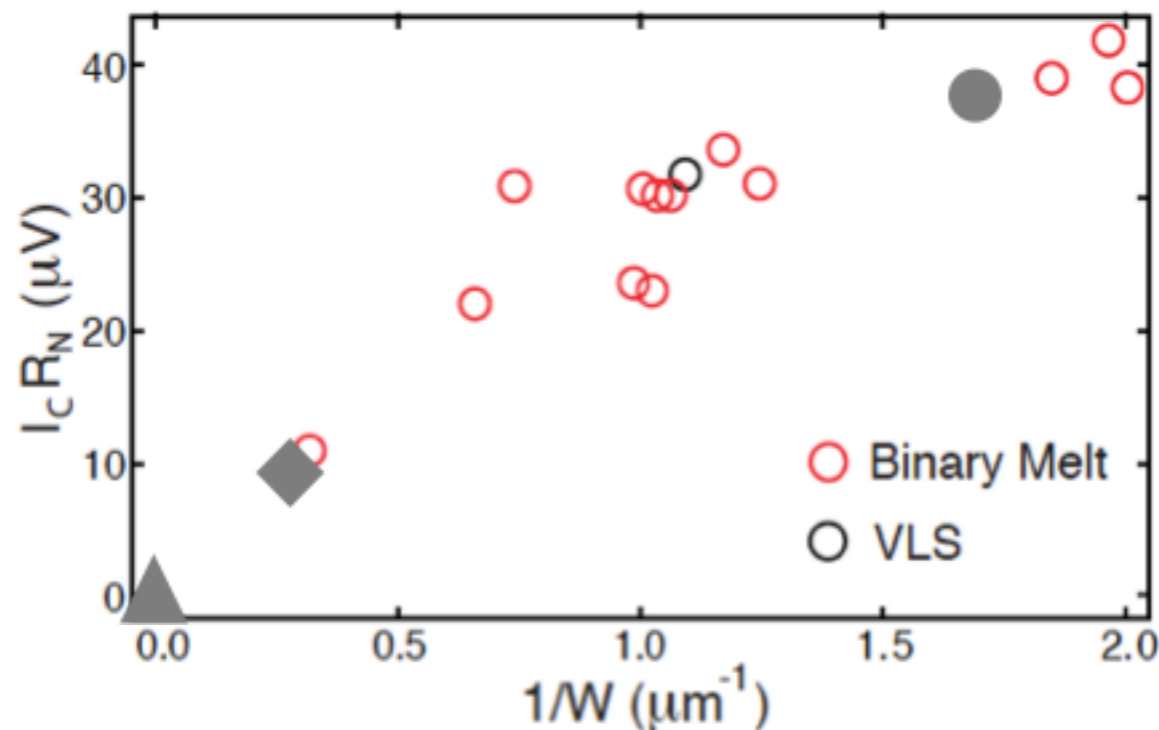


Geometry dependence of V_c

- $I_c R_N \sim 1/W$ over a wide range of devices.



Red curve: $R_N = 51.5 \Omega$
Blue curve: $R_N = 56.1 \Omega$



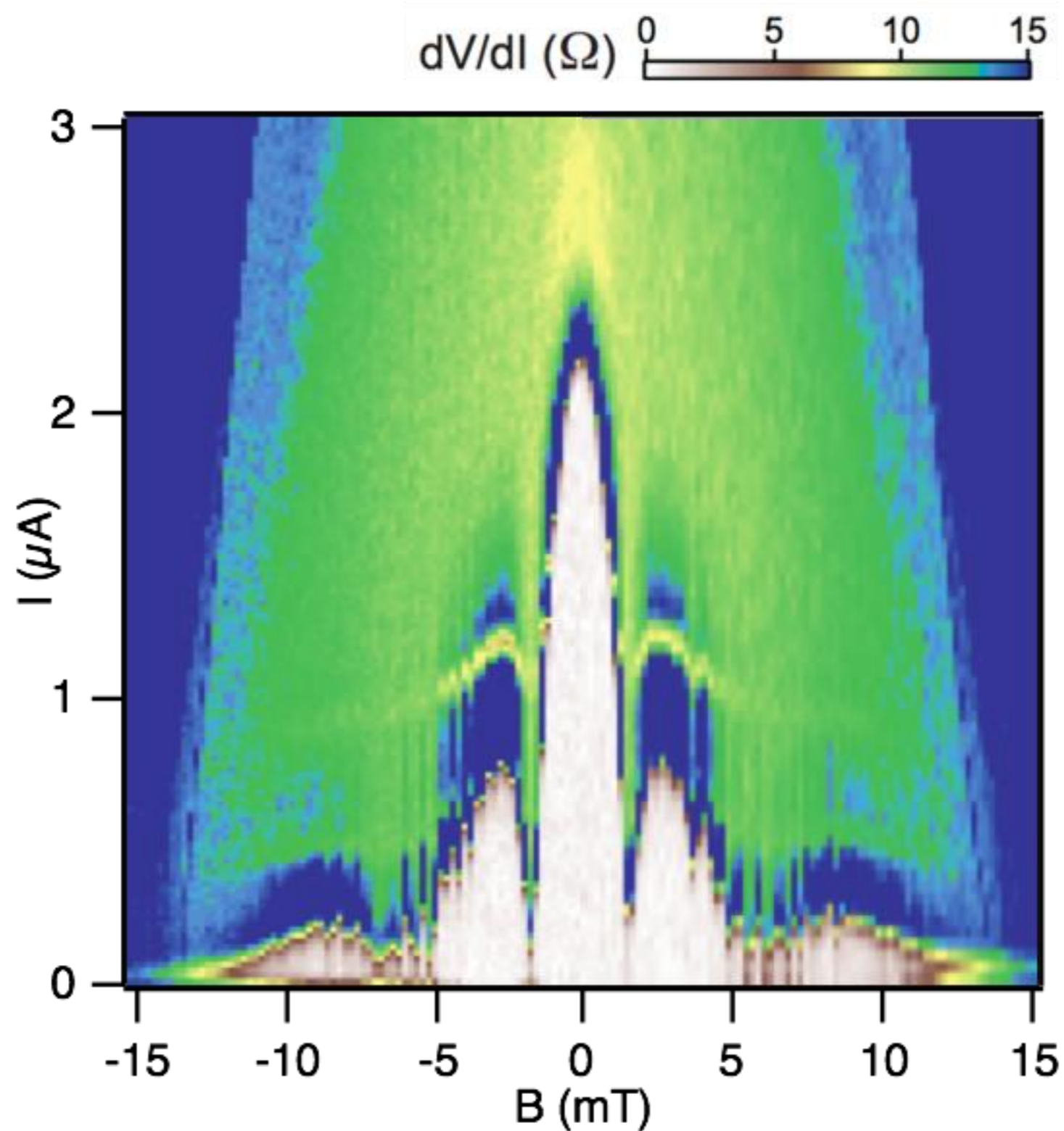
Circle: Zhang *et al.*, PRB, 2011
 Bi_2Se_3 nanowires

Diamond: Sacépé *et al.*, Nat Comm, 2012
Exfoliated Bi_2Se_3

Triangle: Wang *et al.*, PRB, 2012
MBE Bi_2Se_3

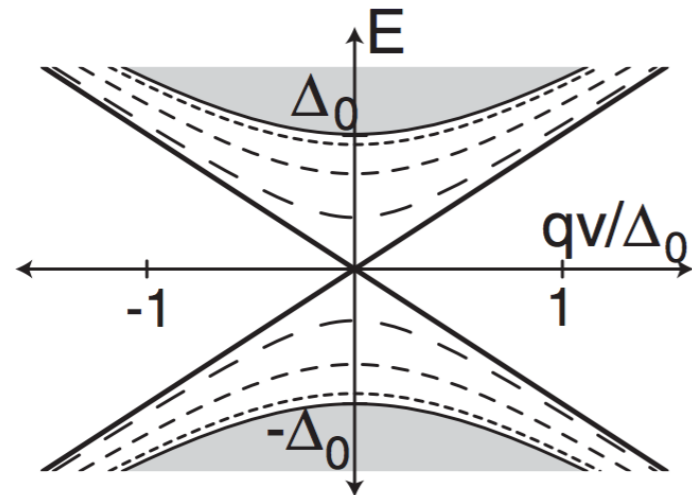
Measured magnetic diffraction pattern

- At first glance appears conventional, but...



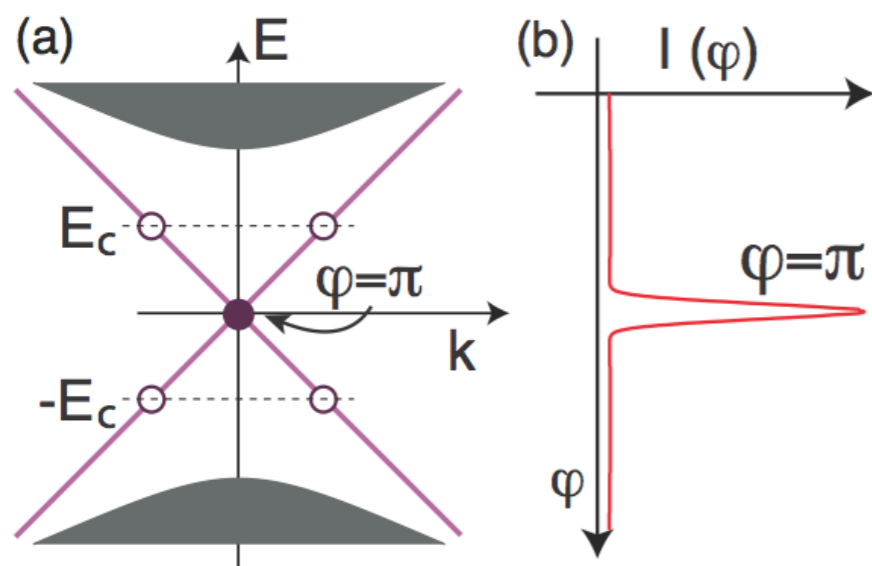
Proposed explanation with Majorana fermions

- Economic, comprehensive, and probably wrong.



1) Take Fu/Kane picture

When phase difference across junction is π , transverse mode is a Majorana state with zero-energy crossing and linear dispersion. Otherwise, gapped and massive.

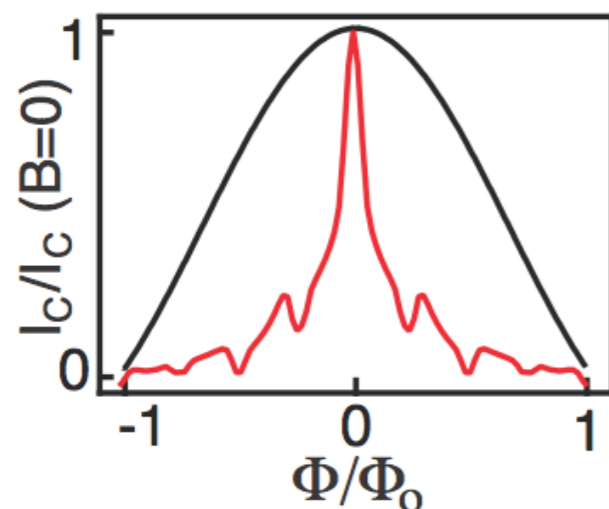


2) Add spatial confinement

Separates topologically-protected neutral state from charged states by confinement energy ($\sim 1/W$).

3) Assume neutral state facilitates supercurrent

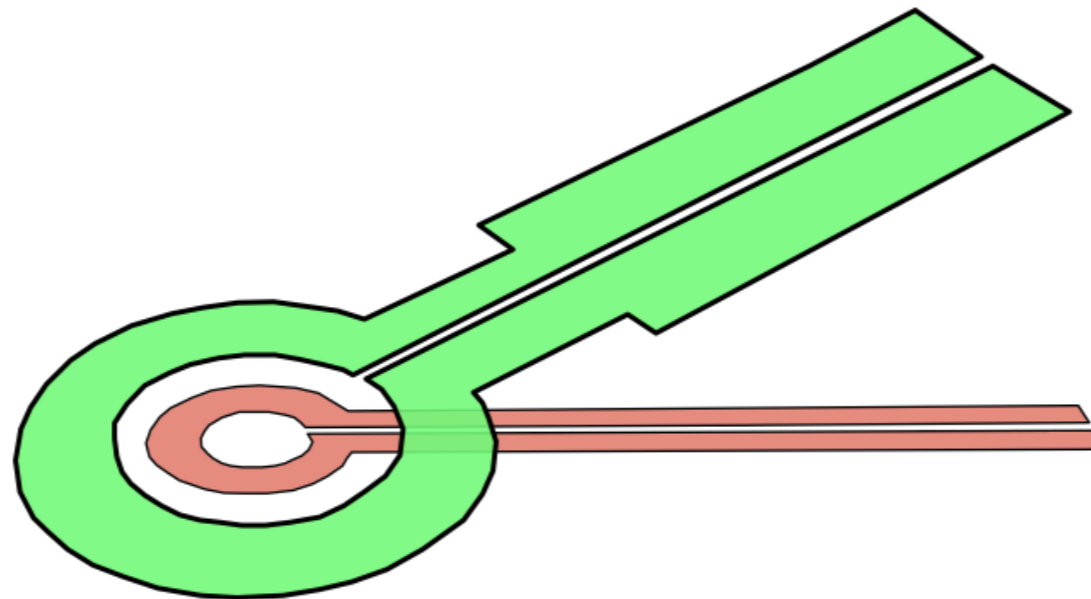
Current-phase relation becomes strongly peaked around particular values of phase, rather than sinusoidal.



4) Magnetic diffraction pattern gains sub- Φ_0 features

Depending on choice of CPR, can calculate aperiodic dips below a flux quantum.

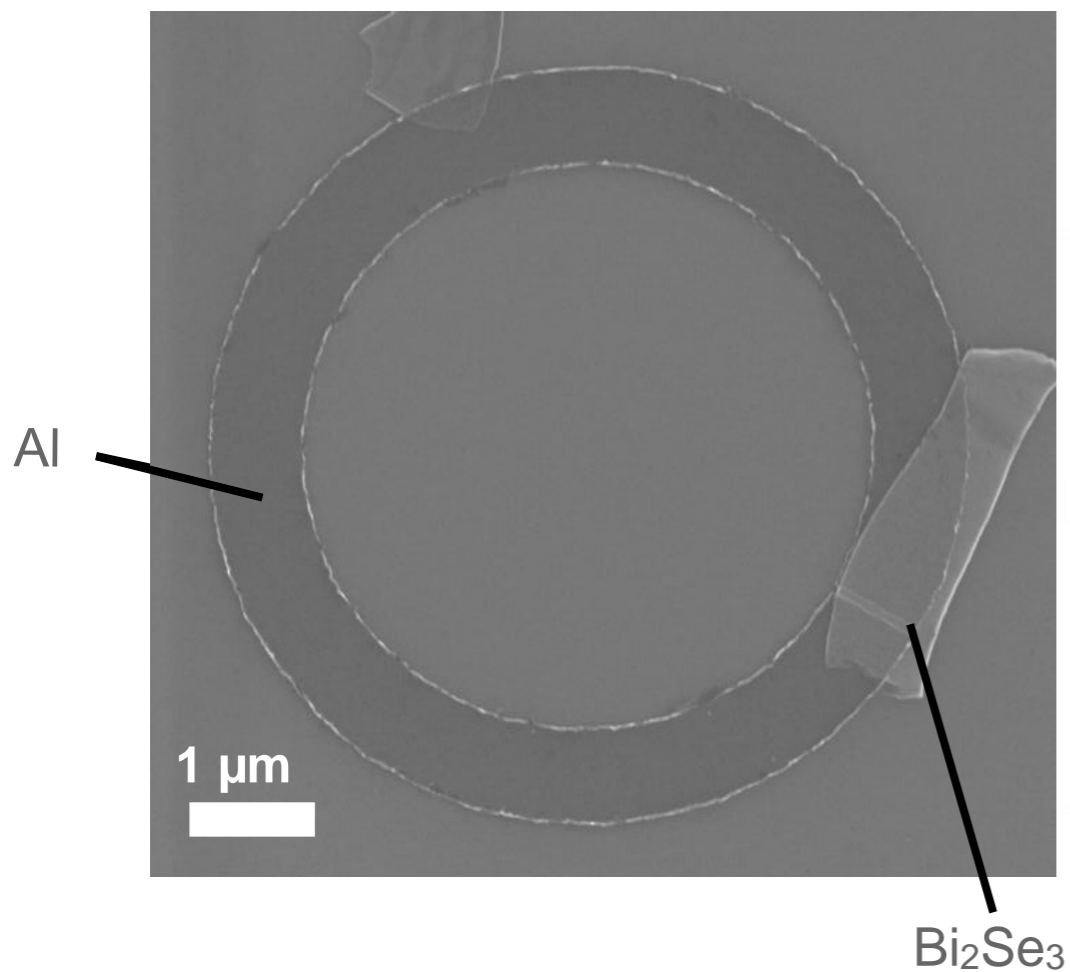
Scanning SQUID Measurements



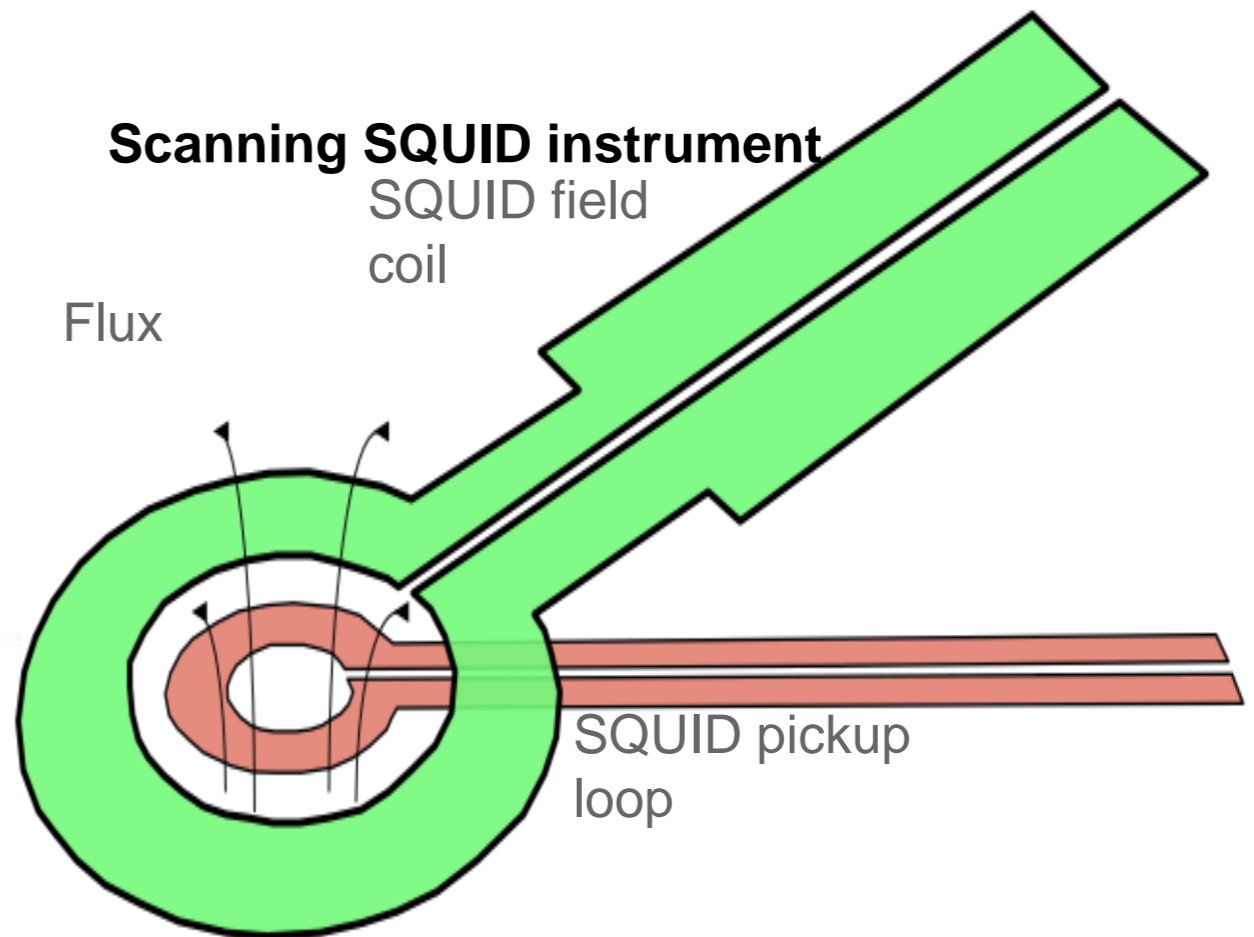
Scanning SQUID measurements

- Local flux detection can directly measure CPR.

Superconductor-TI structures



Scanning SQUID instrument



Huber *et al.*, Rev. Sci. Ins., 2008

Koshnik *et al.*, APL, 2008

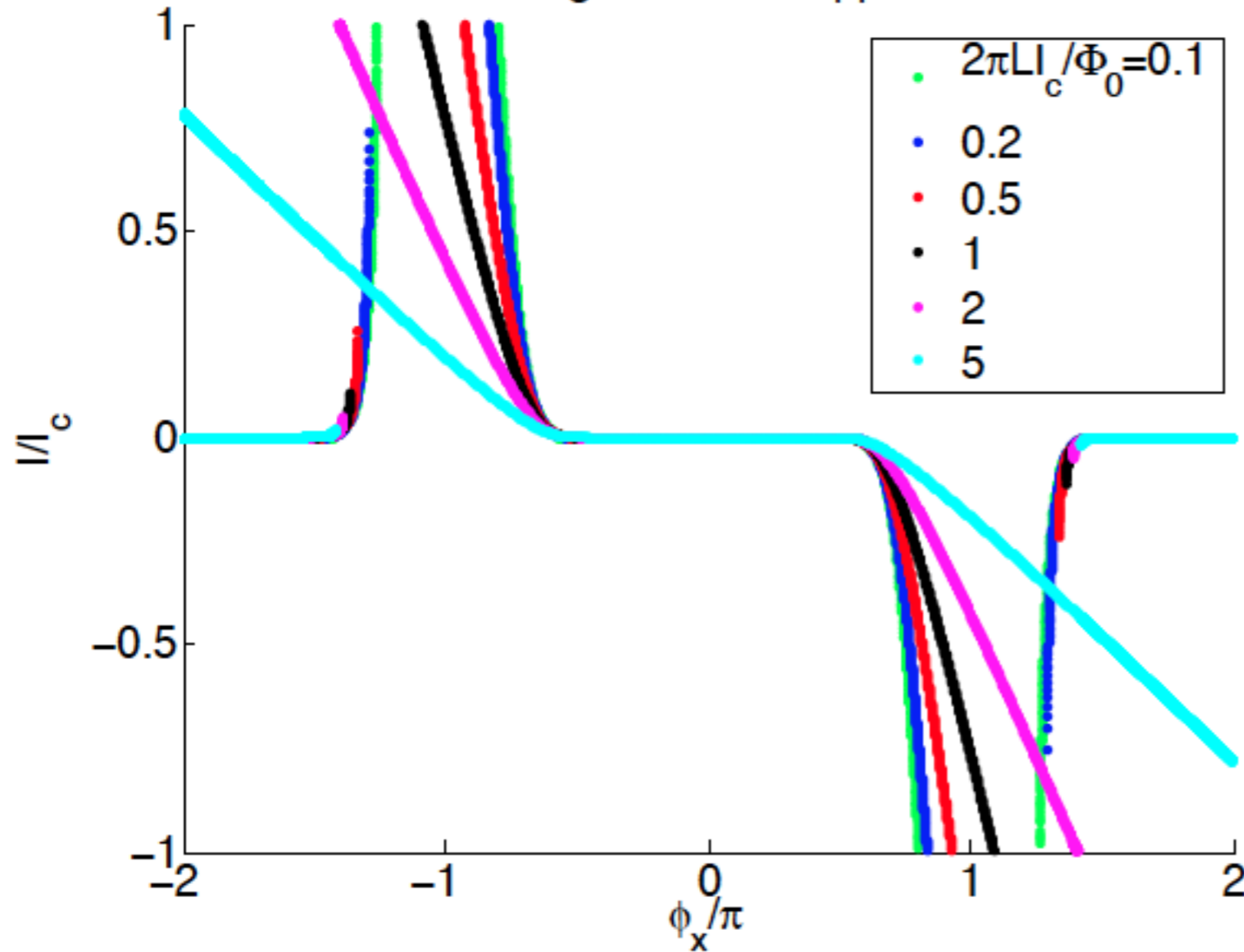
Current-phase relation

$$\Phi_m \sim I_s(\phi)$$

$$\phi \sim 2\pi \Phi_a / \Phi_0$$

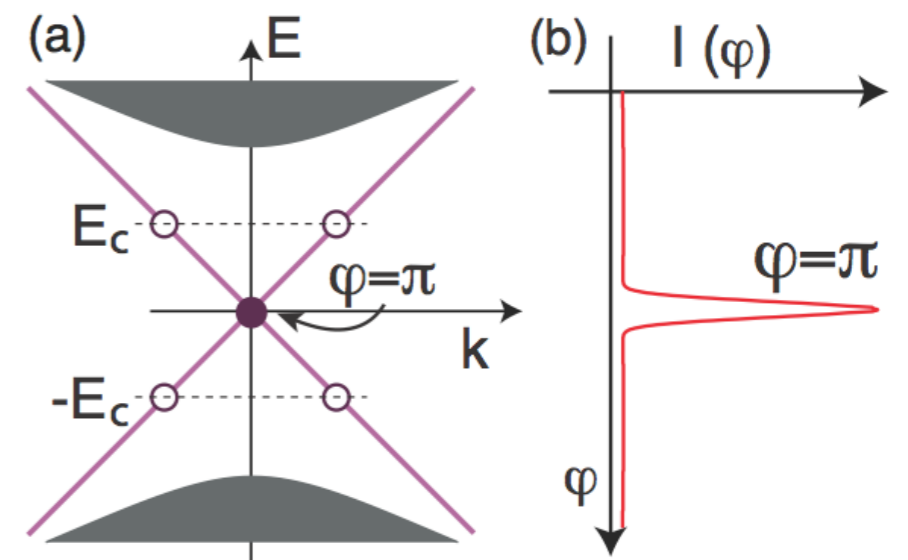
Peaked CPR in SQUID measurements

Circulating current vs applied flux



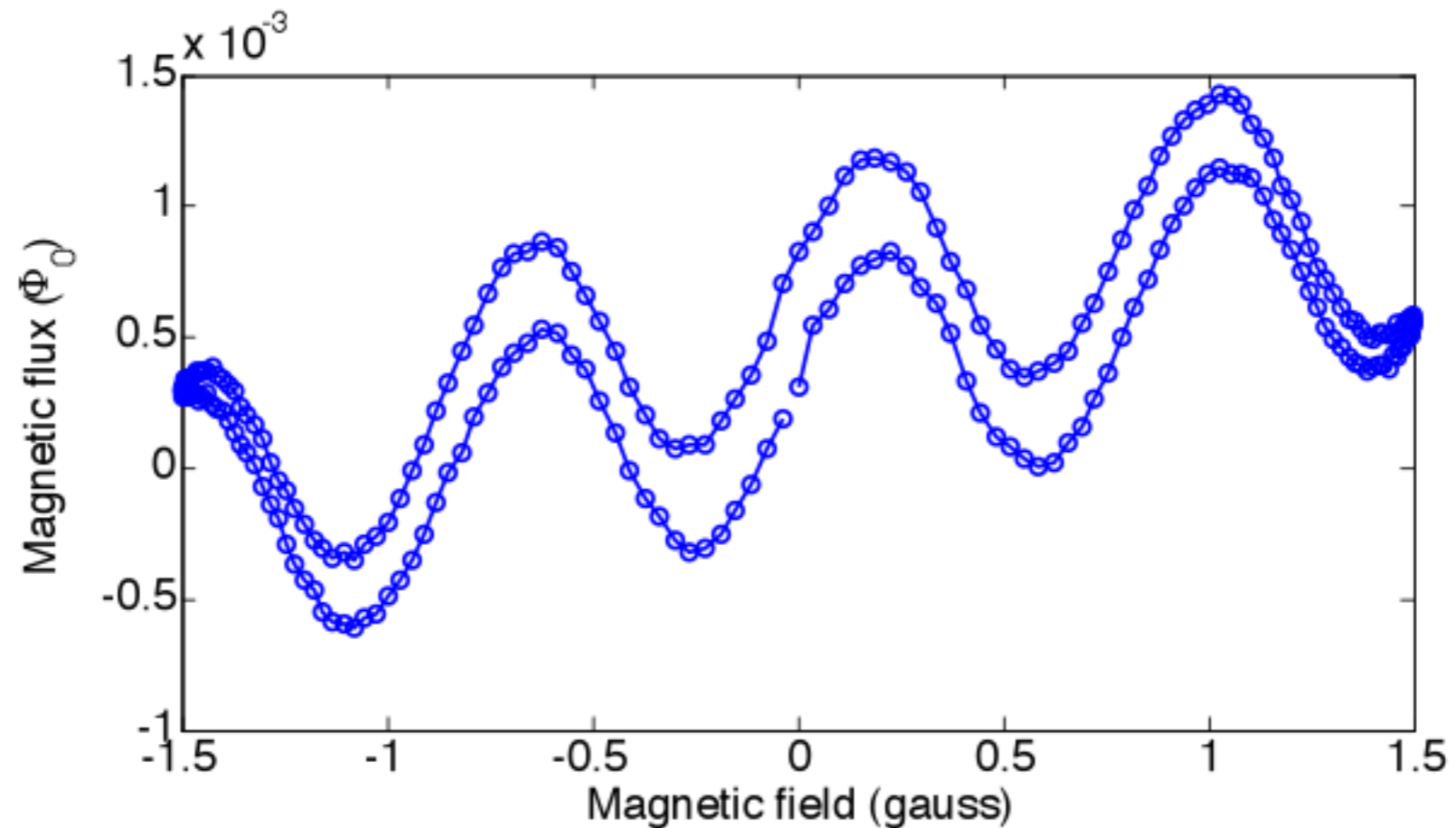
Measuring current phase relations with SQUIDS

A peaked current phase relationship should produce a peaked response of the SQUID response



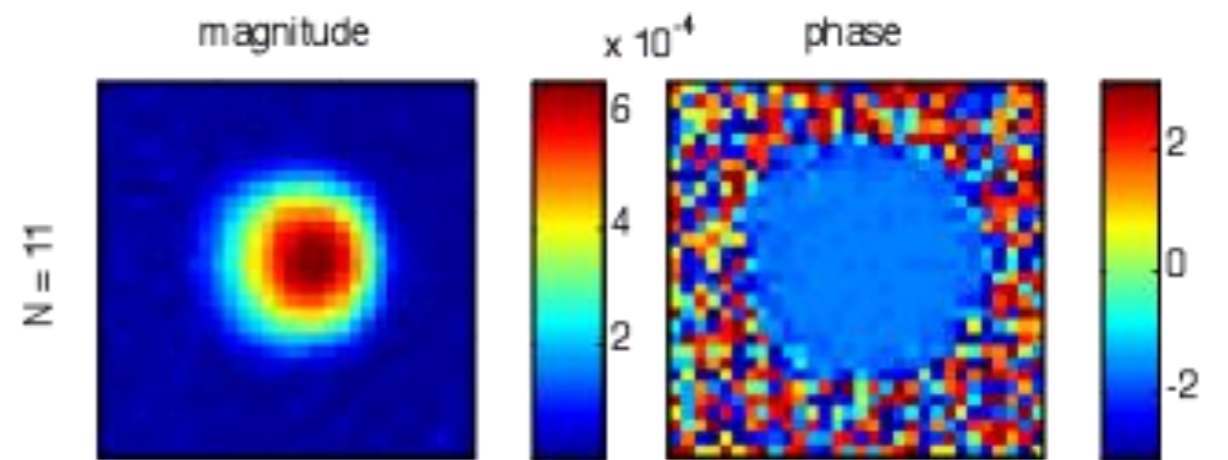
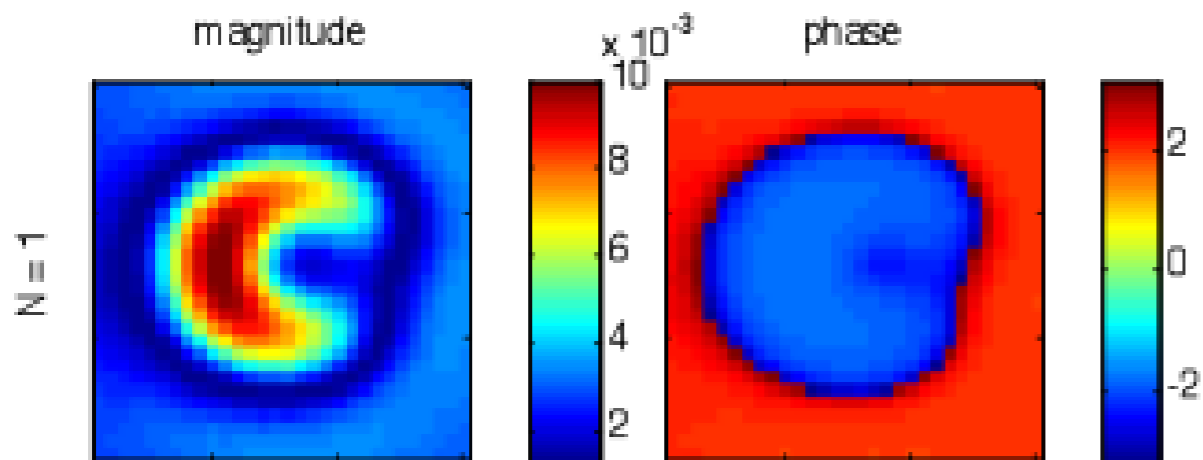
Current-phase relation measurement

- All indications are of a conventional, sinusoidal CPR.



Low-frequency component (bulk)

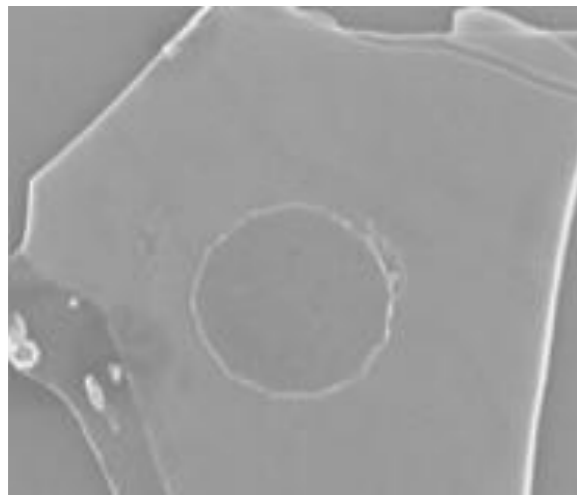
High-frequency component (junction)



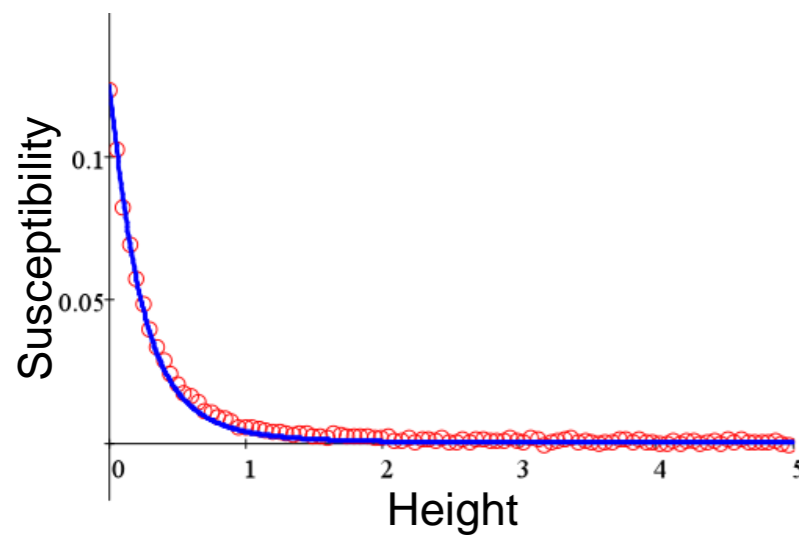
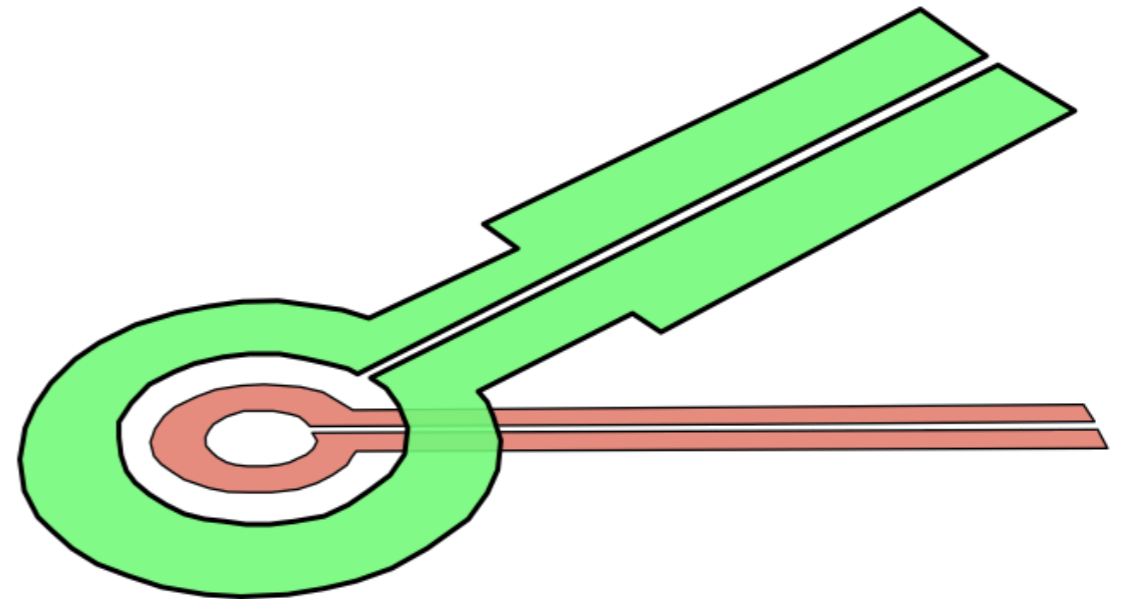
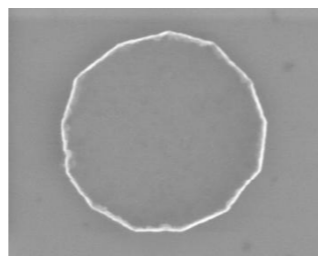
Magnetic penetration depth

- Does proximity to TI dramatically increase penetration?

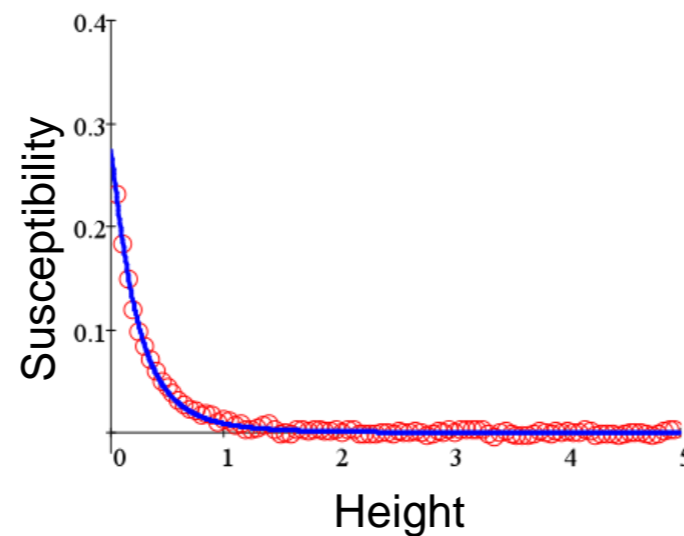
Al dots on Bi_2Se_3



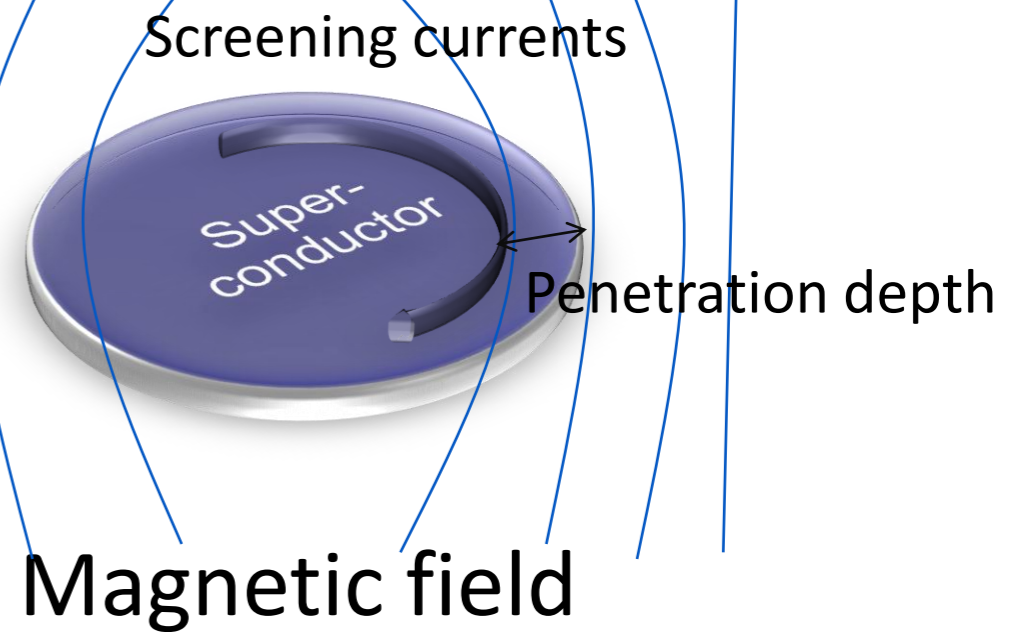
Al dots on substrate



$\lambda \sim 62 \text{ nm} - 3.2 \mu\text{m}$

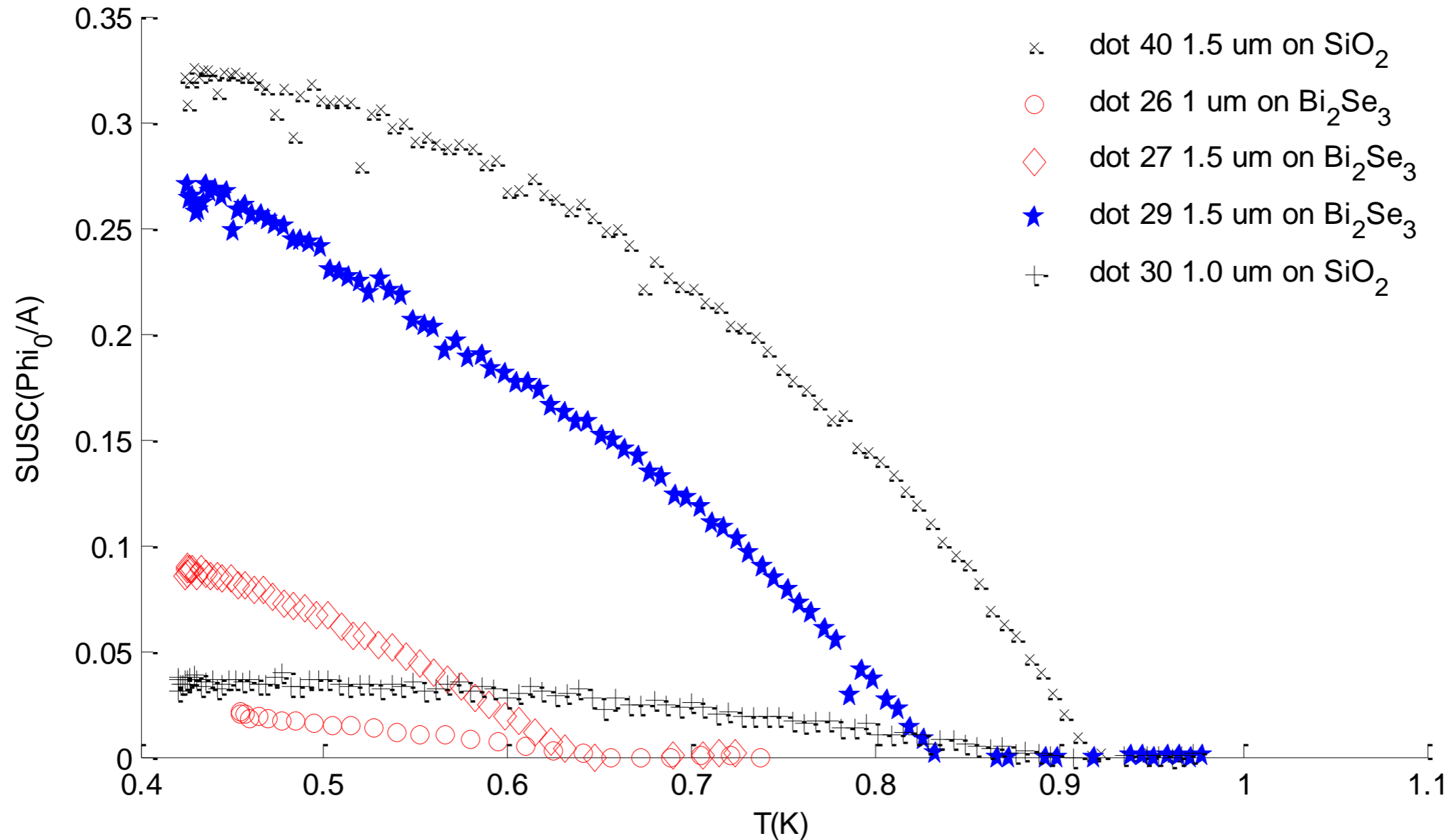


$\lambda \sim 19 \text{ nm} - 1.4 \mu\text{m}$

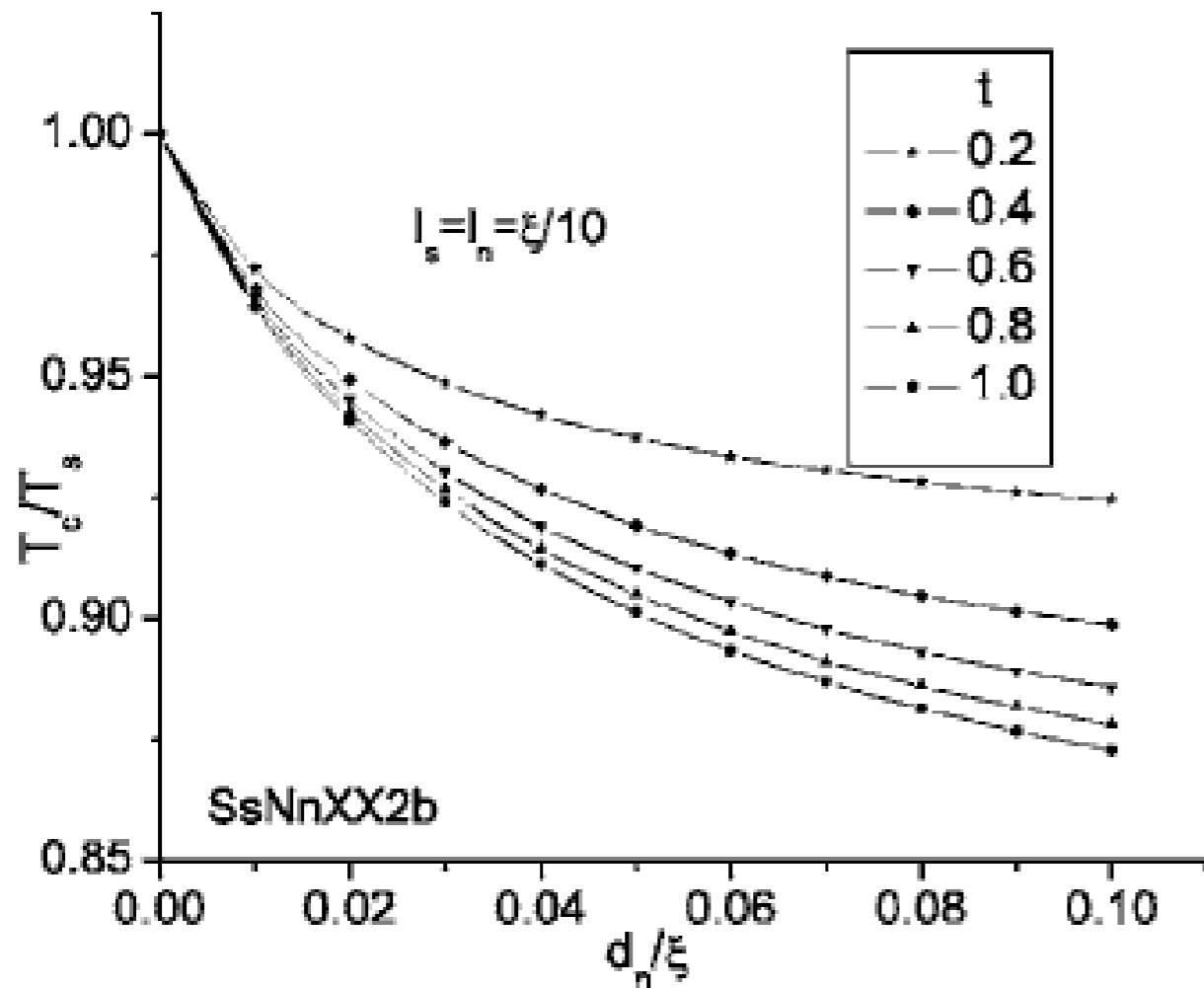


T_C of Aluminum dots on Bi_2Se_3

- Does proximity to TI decrease the transition temperature?



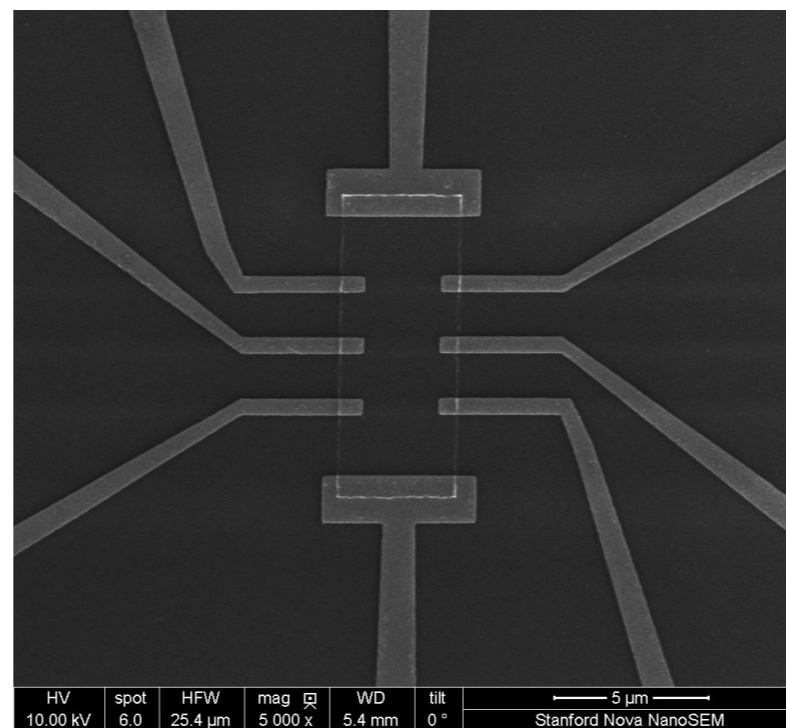
Comparison to metals



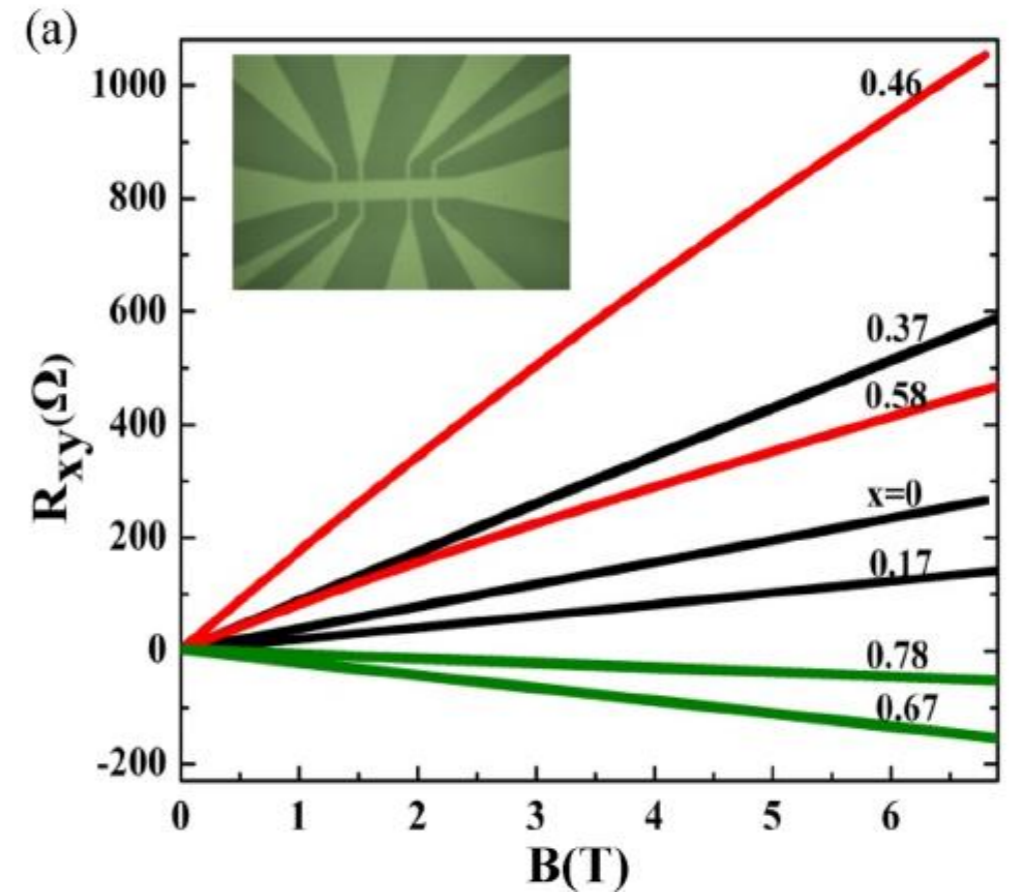
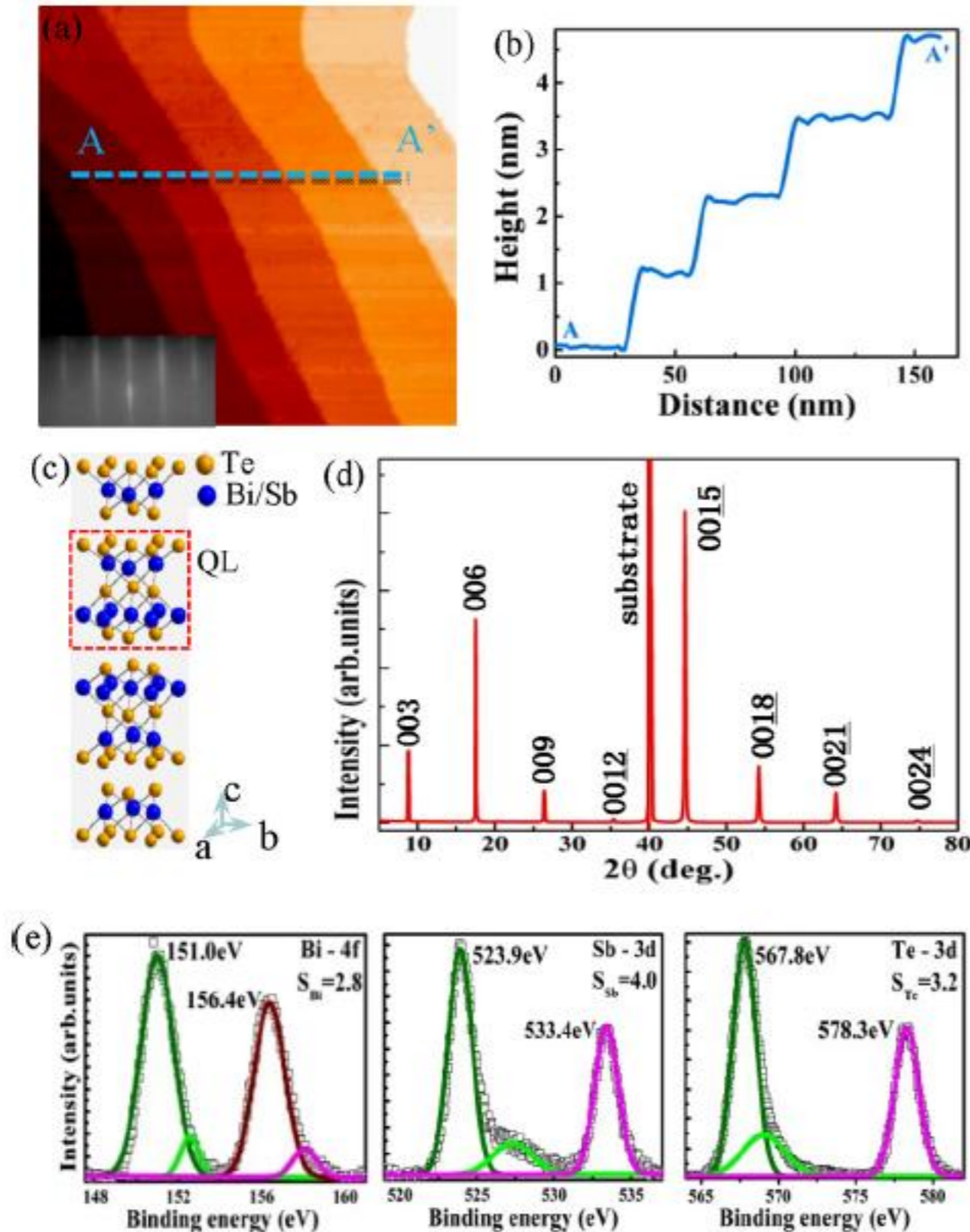
- The proximity effect can account for the reduction of T_c , but only if the DOS in the TI is similar to that of a metal
- What effect does strong spin-orbit have on the proximity effect
- Can this help explain the soft gap observed in nanowire experiments

$$S_{sn} = \frac{d_s}{T_{c0}} \left| \frac{dT_c}{dd_n} \right| = \Gamma_{sn} \frac{N_n}{N_s}.$$

Tunable Transport in MBE-grown BiSbTi_3



Growth of TI MBE $(\text{Bi}_{1-x}\text{Sb}_x)_2\text{Te}_3$ Films – IOP, Chinese Academy of Science

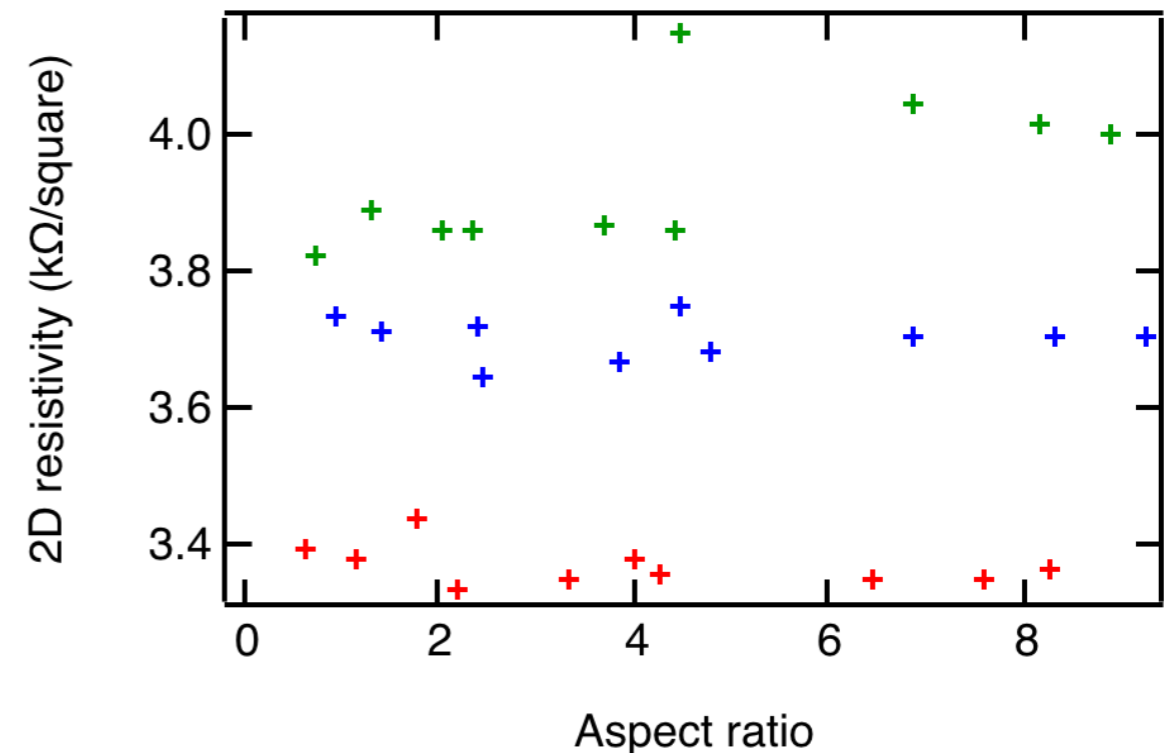
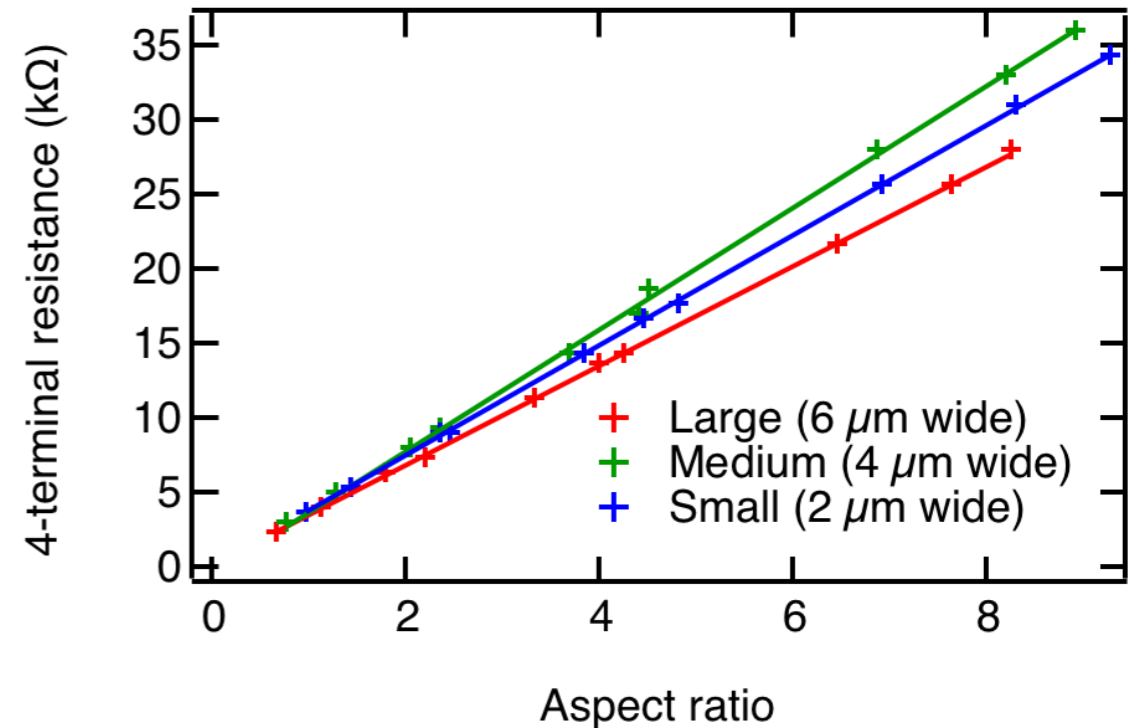
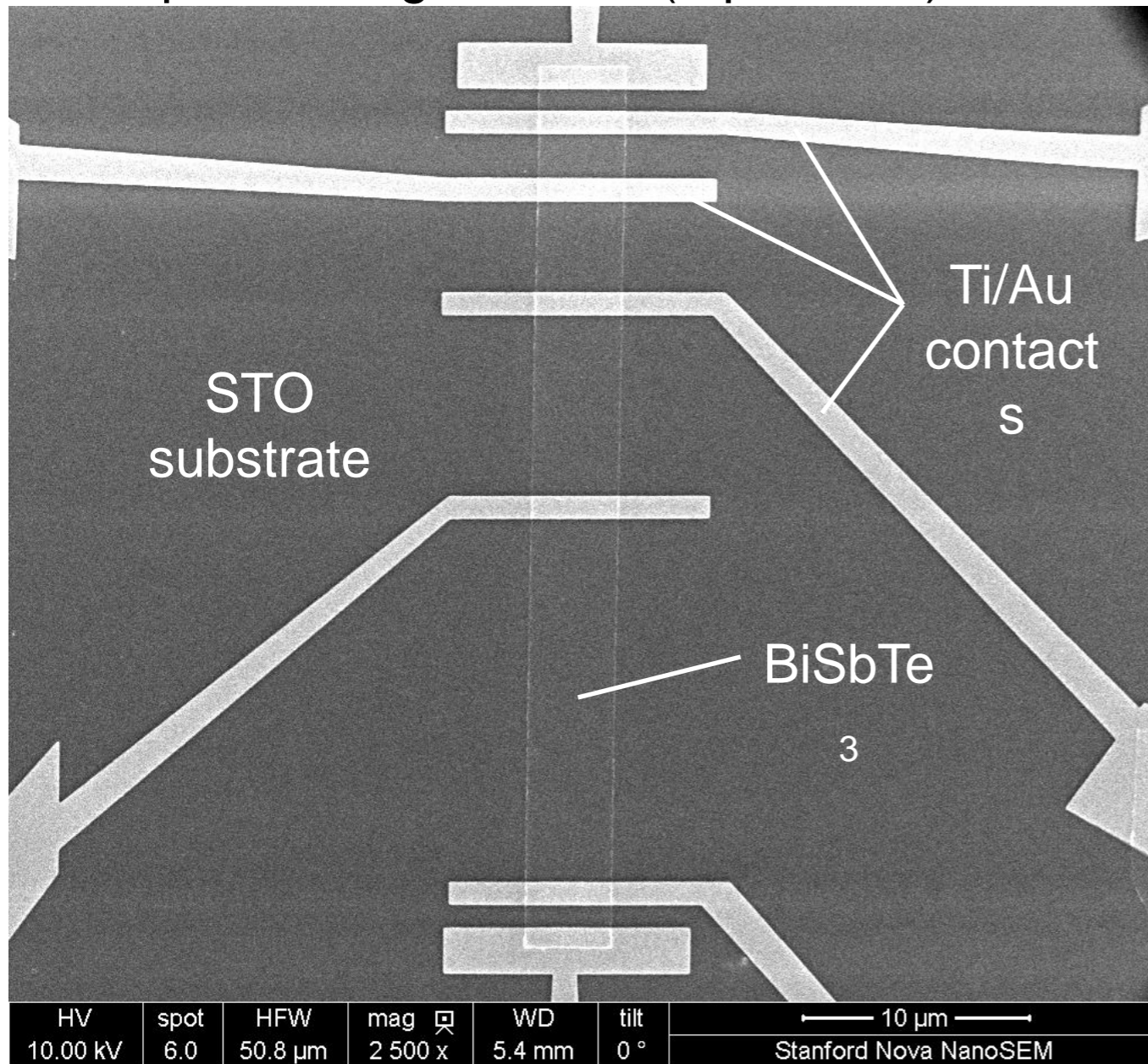


- Our films: $x=0.5$ and thickness=10nm

Surface or Edge Conductance?

- Resistance appears to scale with aspect ratio, not length

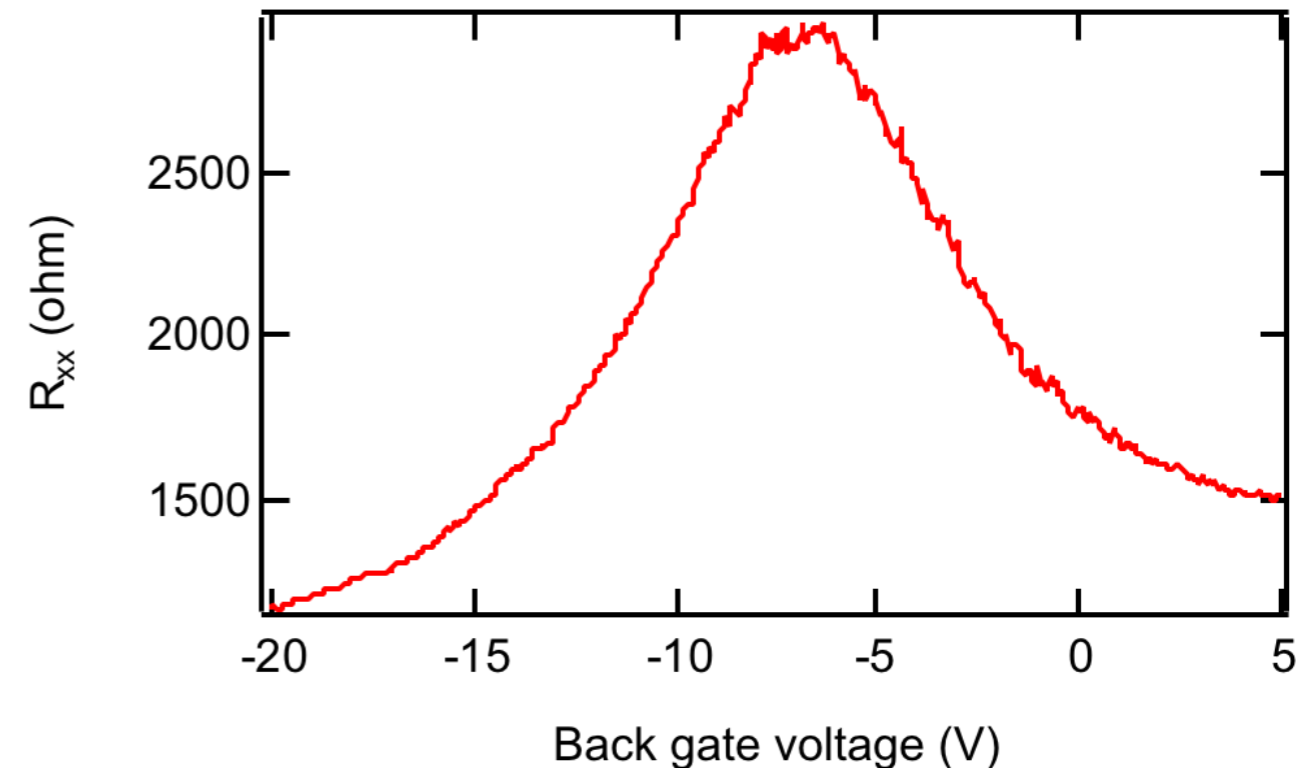
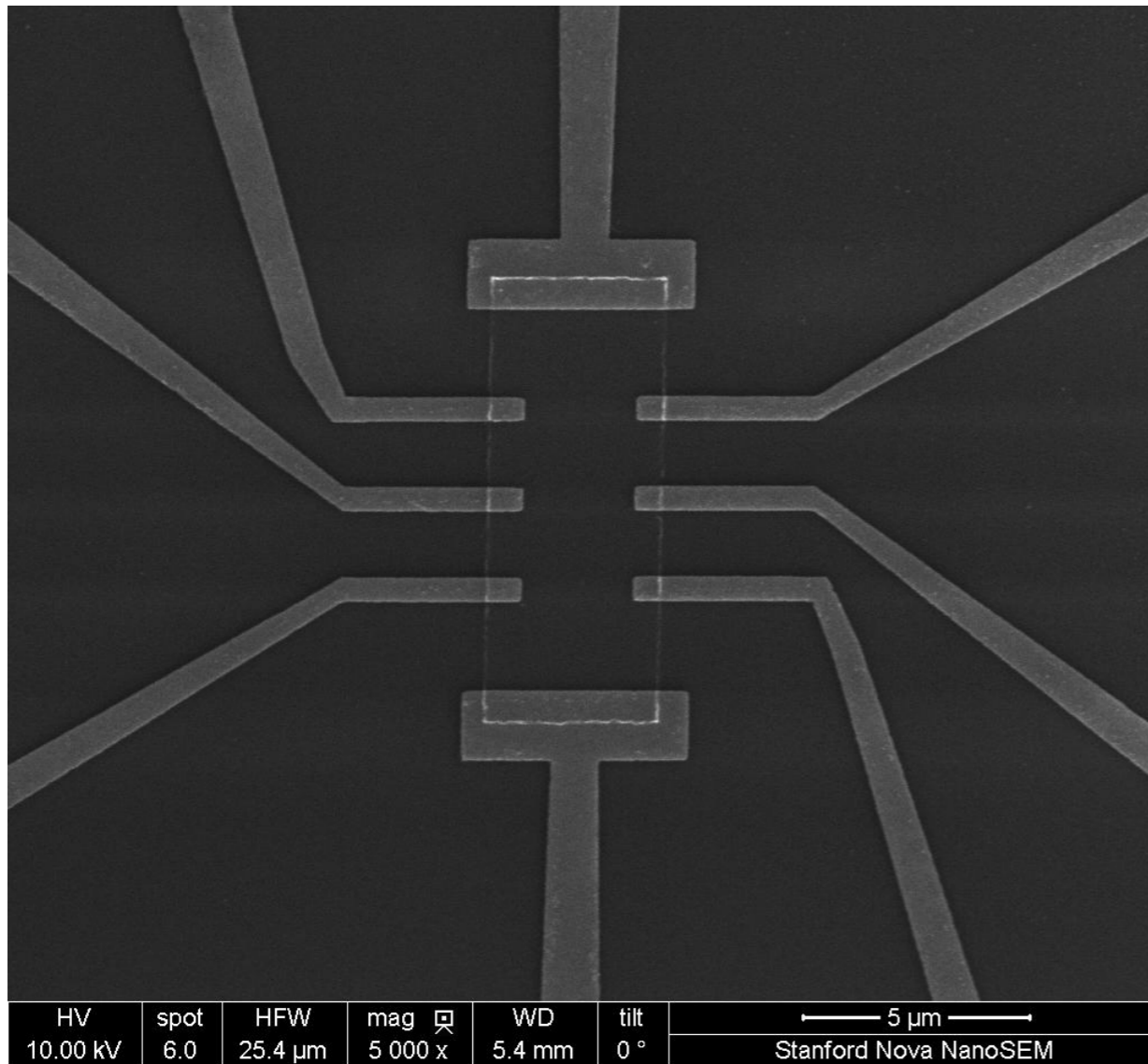
Example rectangle device (4 μm wide)



(Typical contact resistance $\sim 1\text{-}1.5 \text{ k}\Omega$)

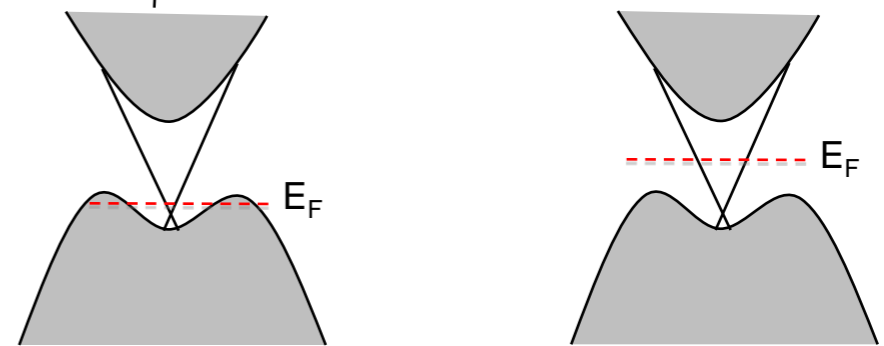
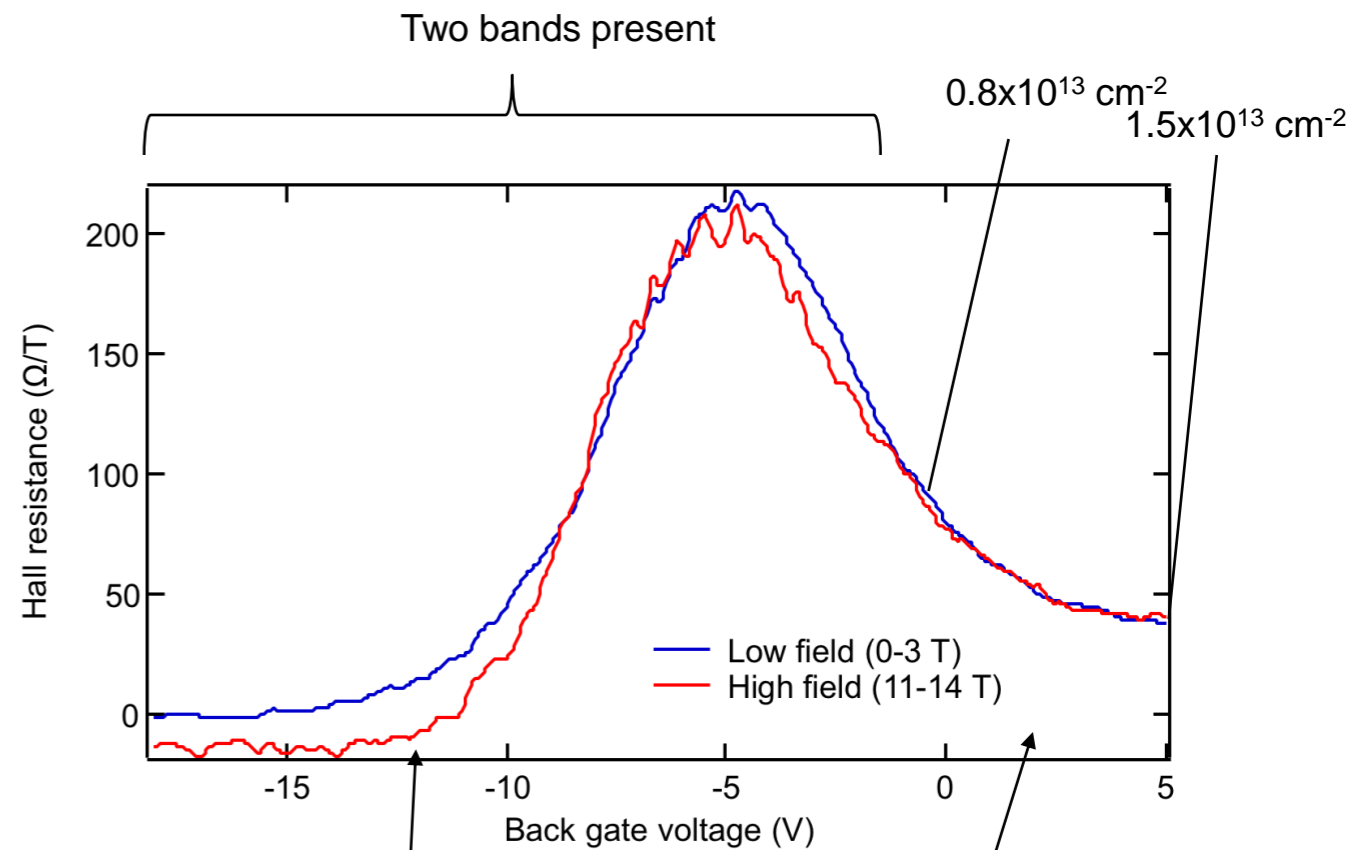
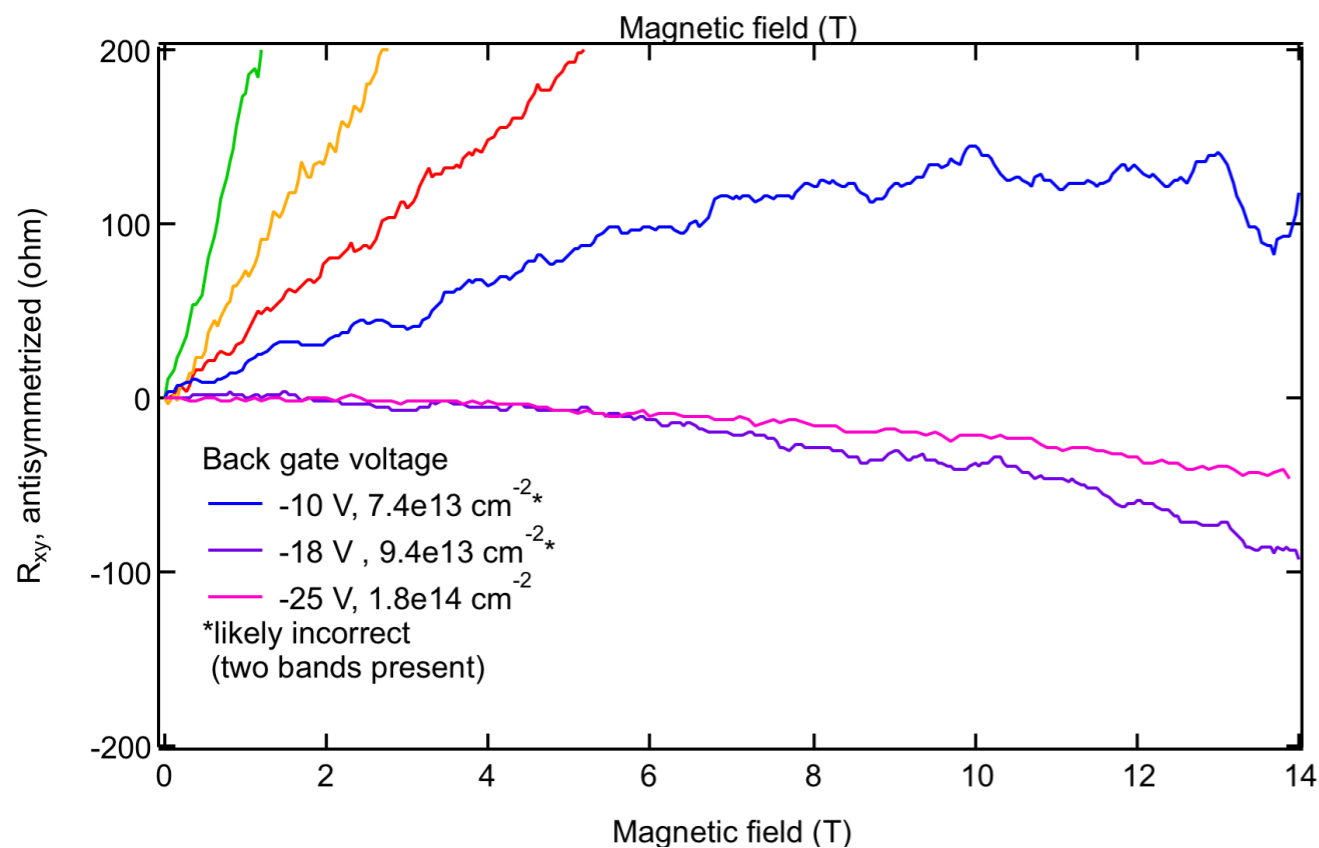
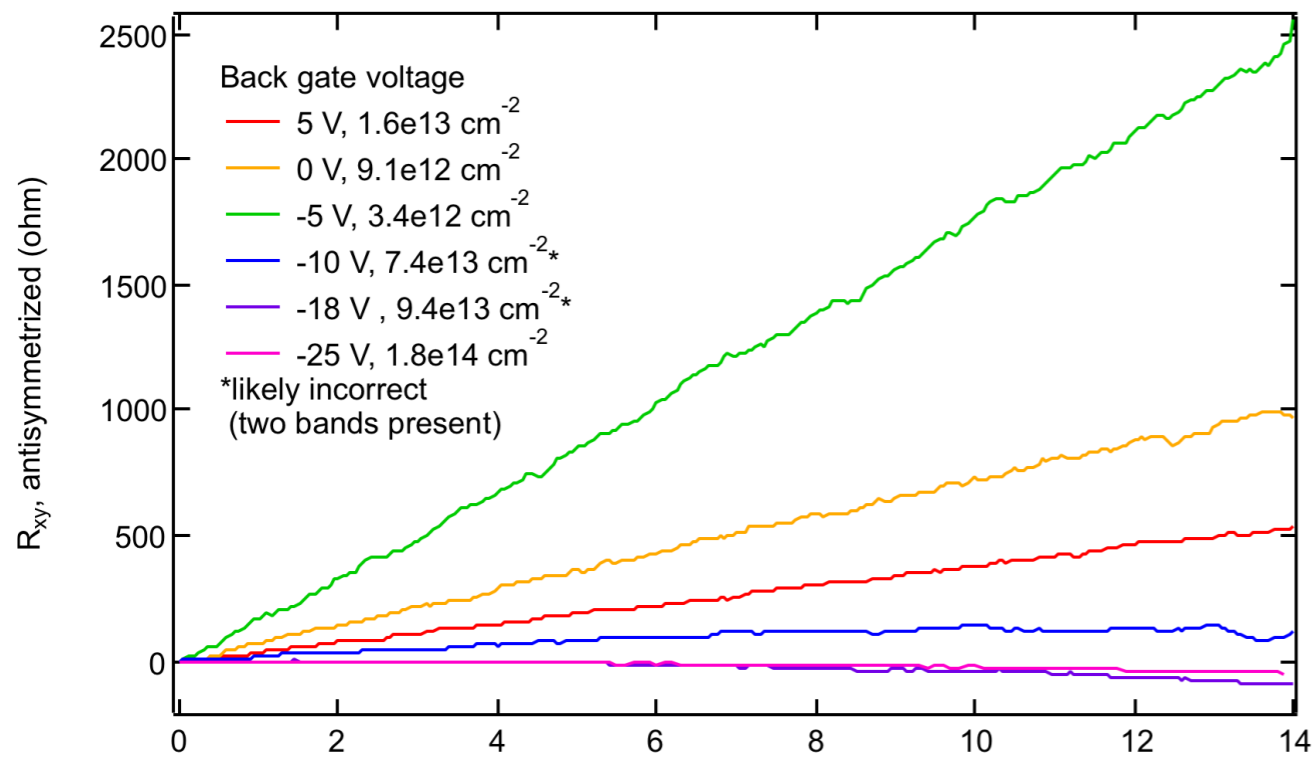
Hall Bar Device

- Conduction tunable with a gate, peaks in R regularly achieved



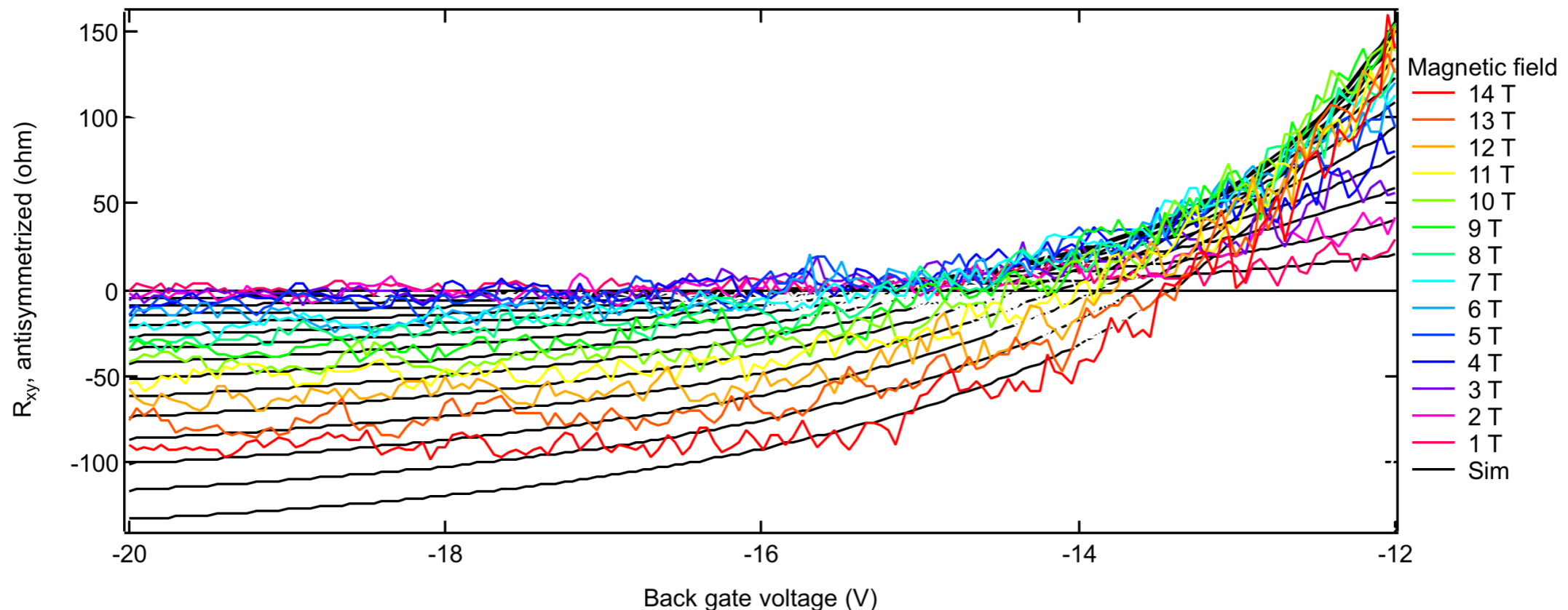
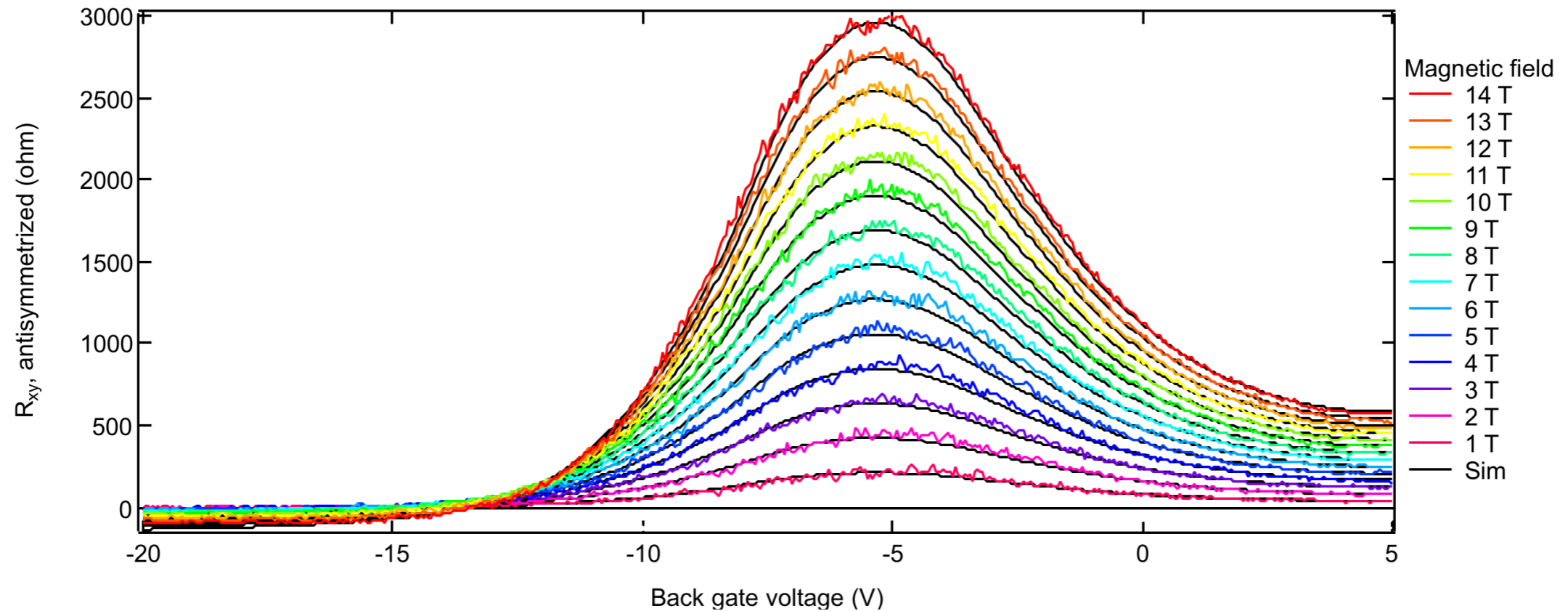
Hall Resistance

- Ambipolar transport achieved at negative backgate voltages



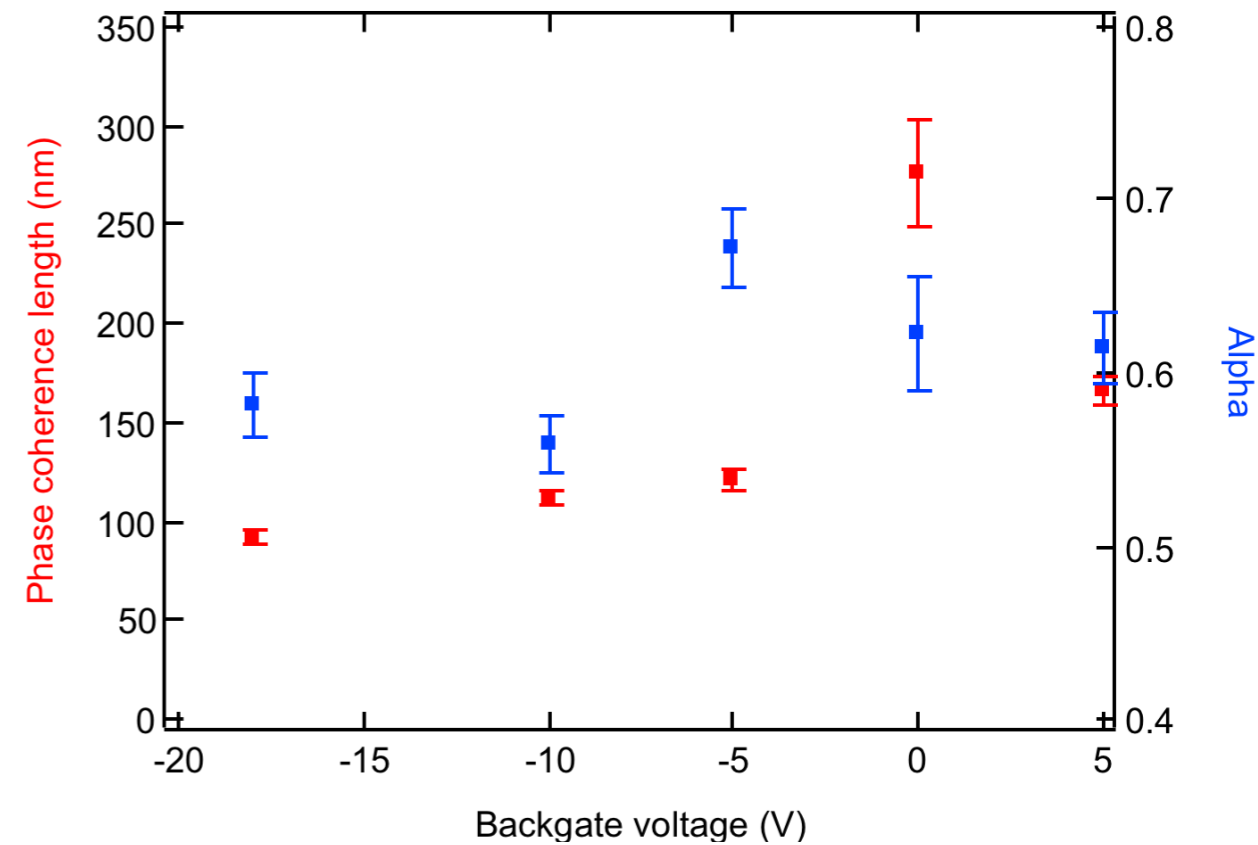
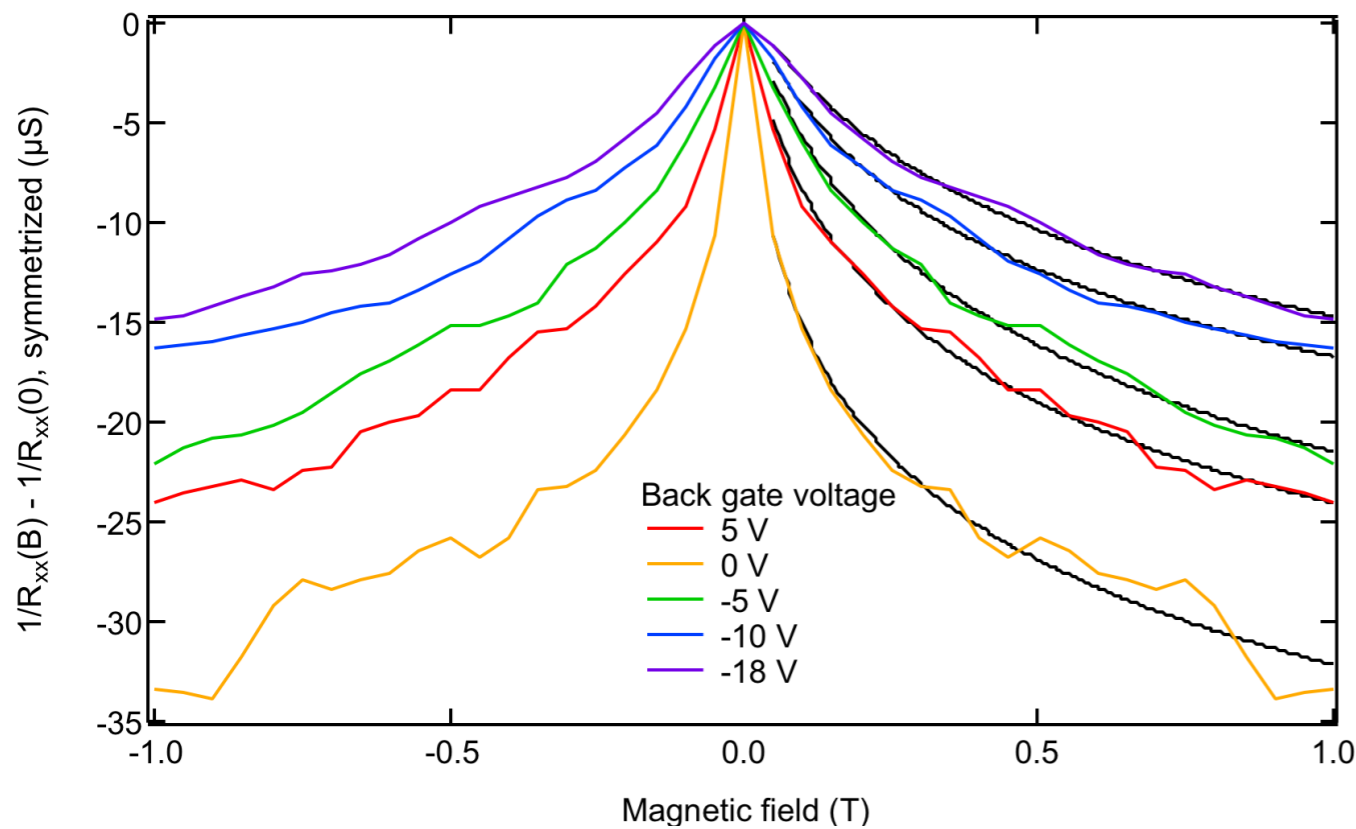
Simulation vs. Hall Data

- Fits very good, until more negative gate voltages



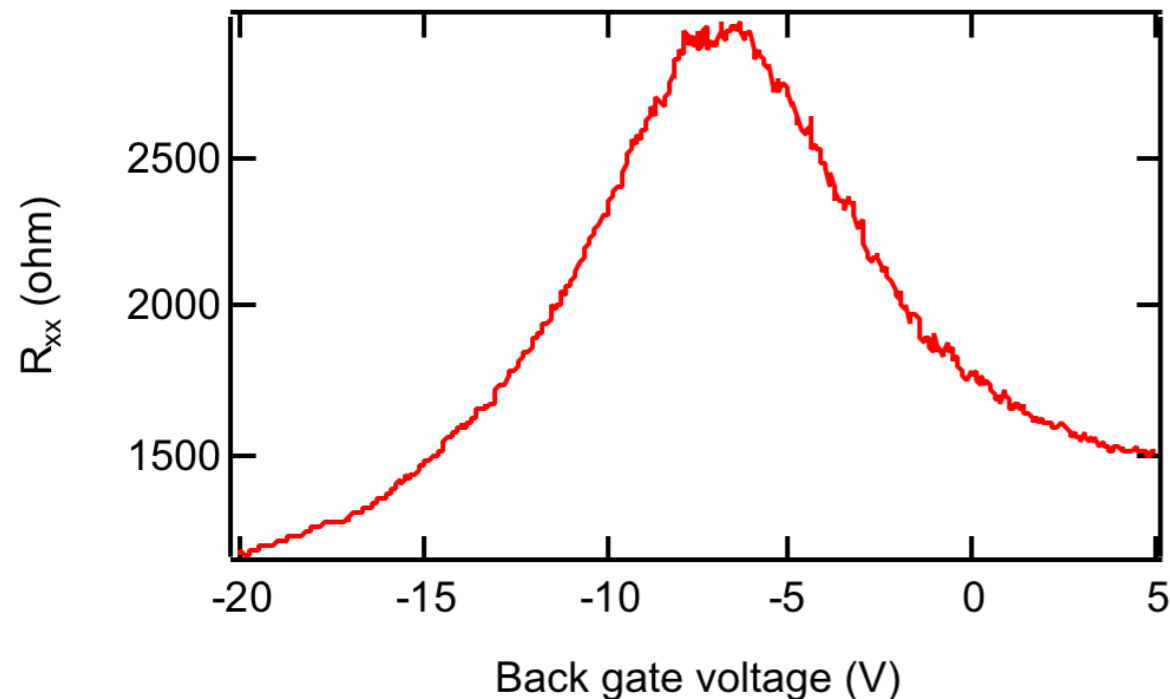
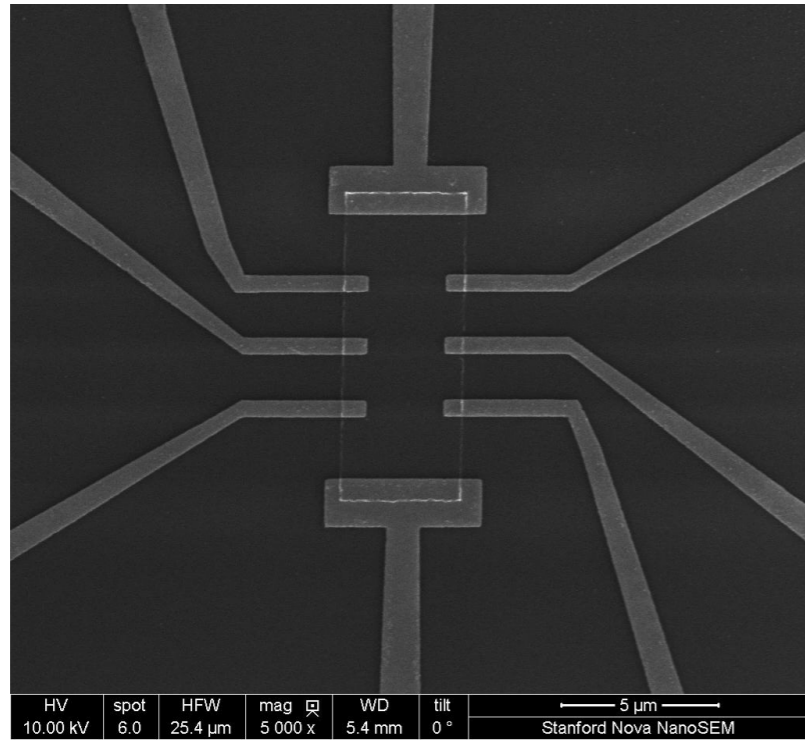
Weak anti-localization

- Fits to HLN, extraction of spin-orbit strength and phase-coherence length



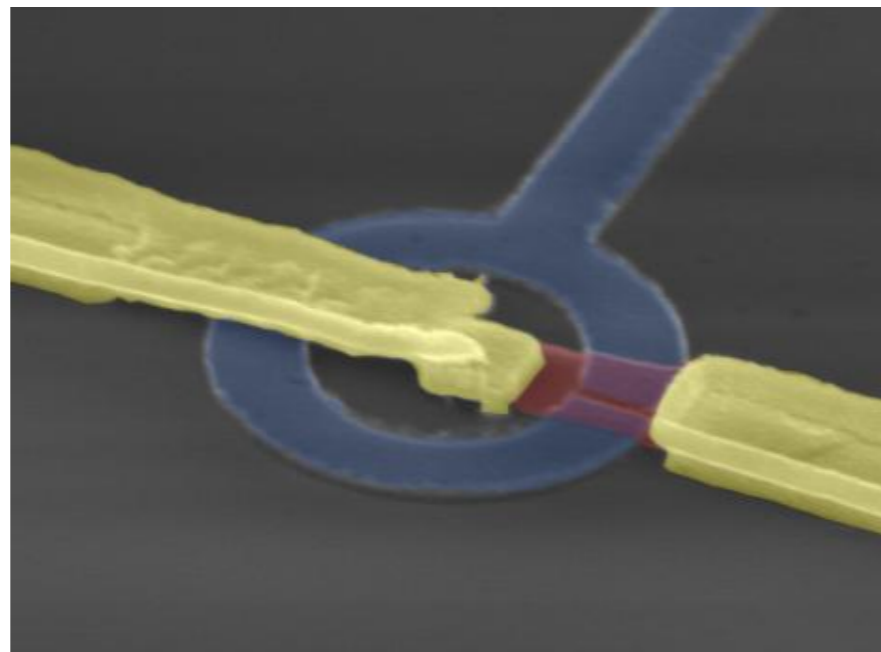
$$\Delta\sigma \approx \alpha \frac{e^2}{2\pi^2\hbar} \left(\ln \left(\frac{B_\phi}{B} \right) - \psi \left(\frac{1}{2} + \frac{B_\phi}{B} \right) \right)$$

Transport in MBE-grown TI films



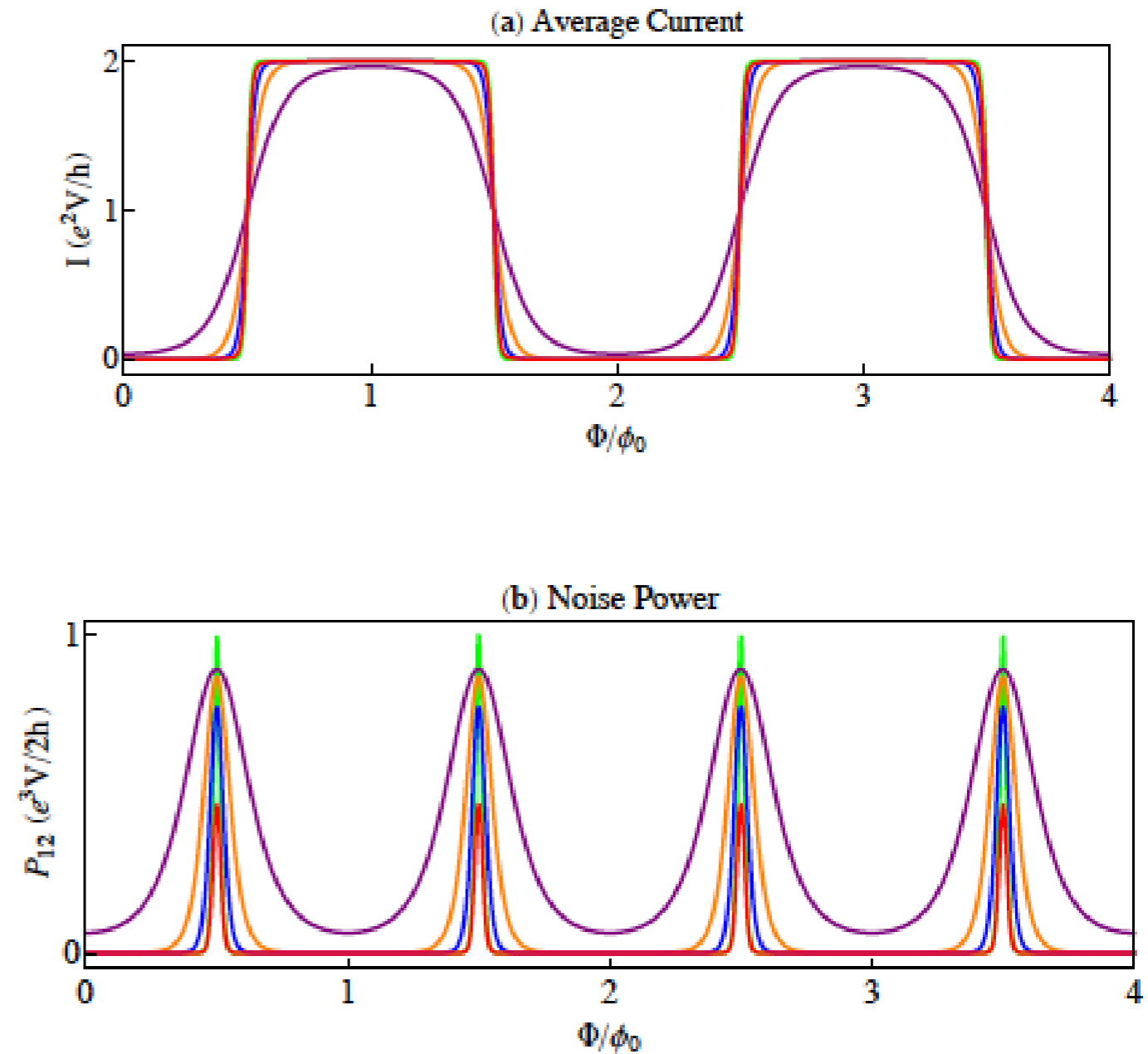
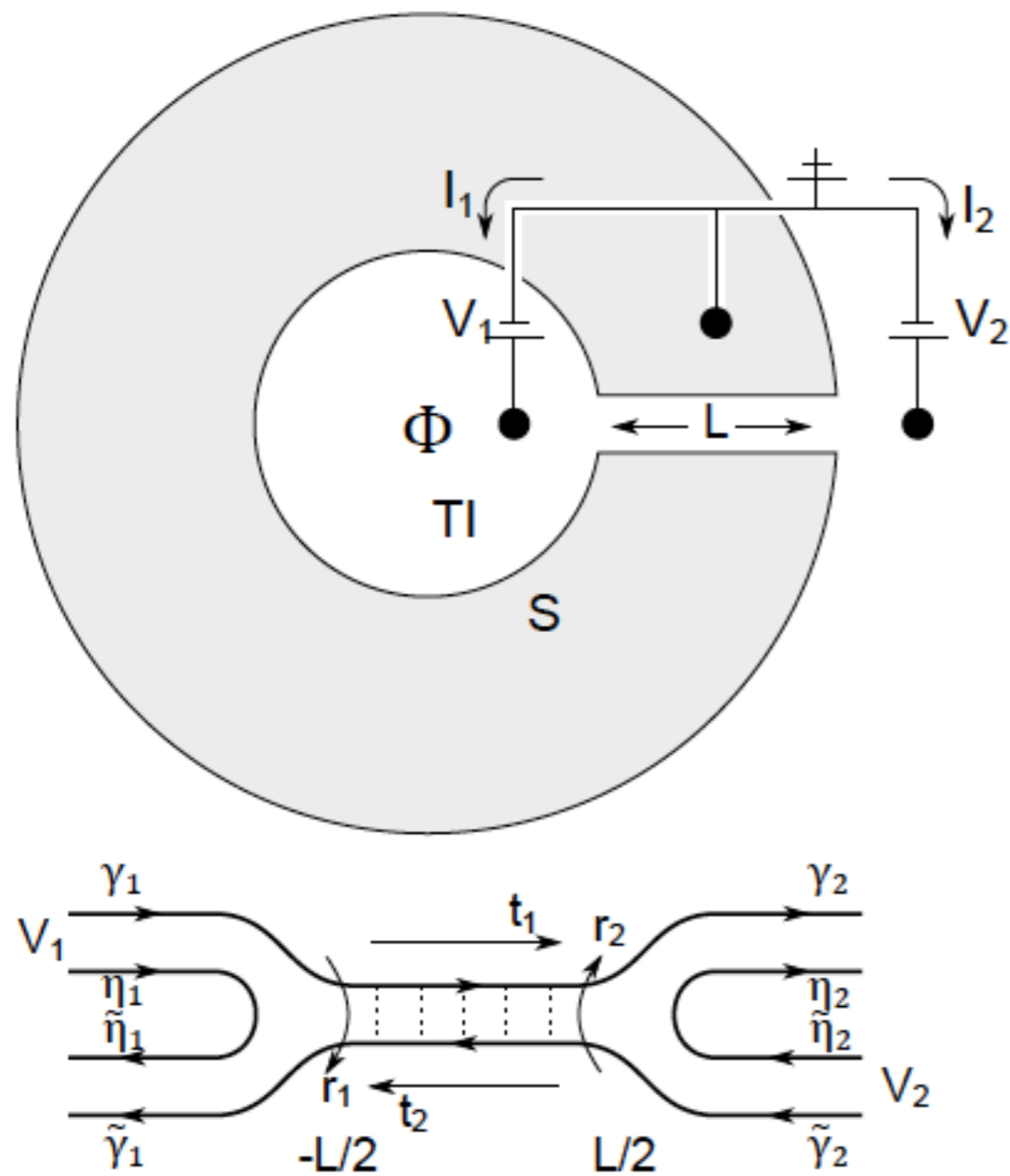
- Can tune through the ambipolar (“Dirac”) point in this material and can do it routinely
- Can understand the shape of the Hall resistance and use it to get both electron and hole densities/mobilities
- Mobility current low (500 cm^2/Vs). Growers have improved the surface morphology and have succeeded in capping the surface

New Measurements



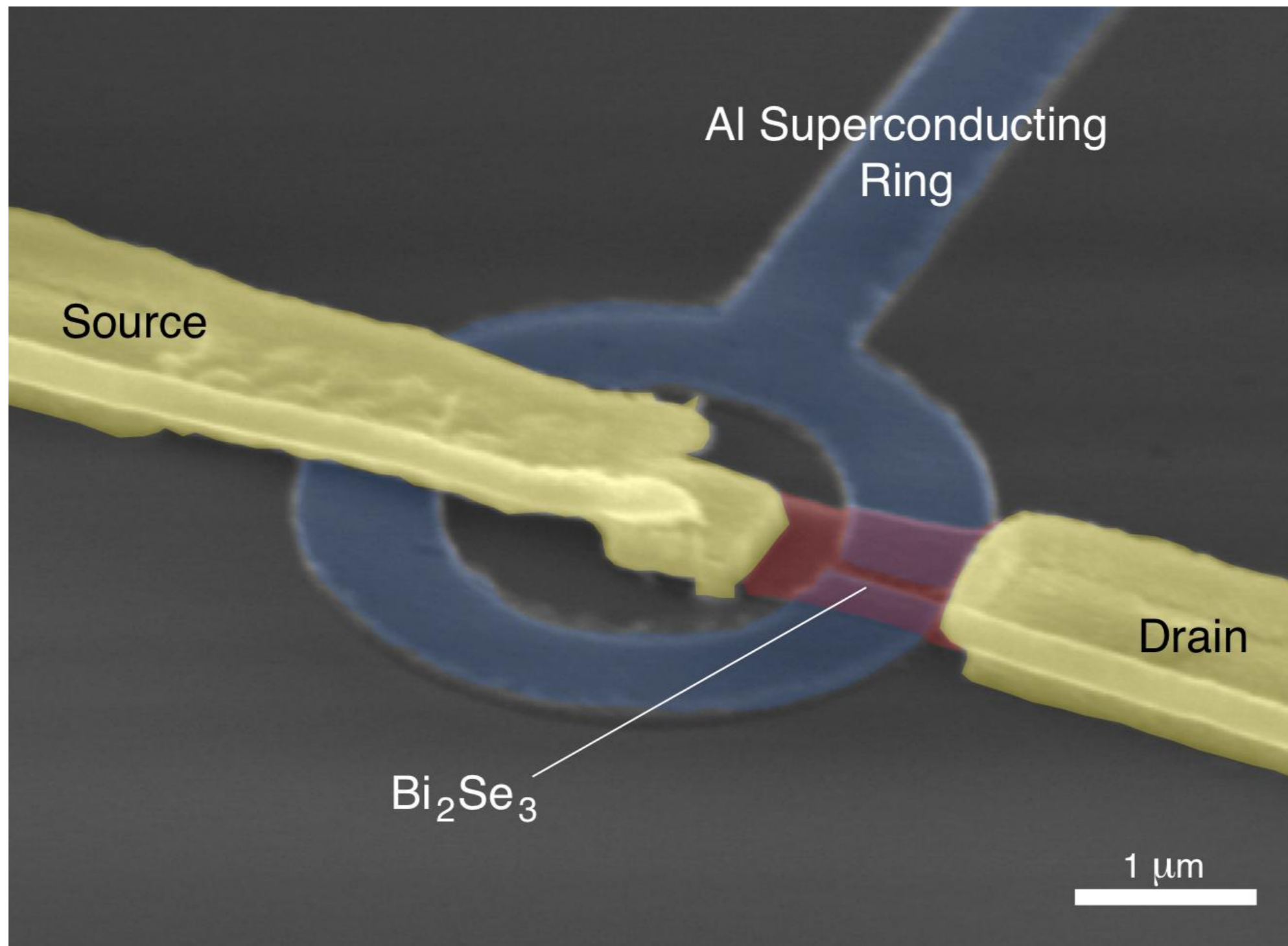
Measuring Transport Along Junctions

- Work from Wieder, Zhang and Kane – coming soon



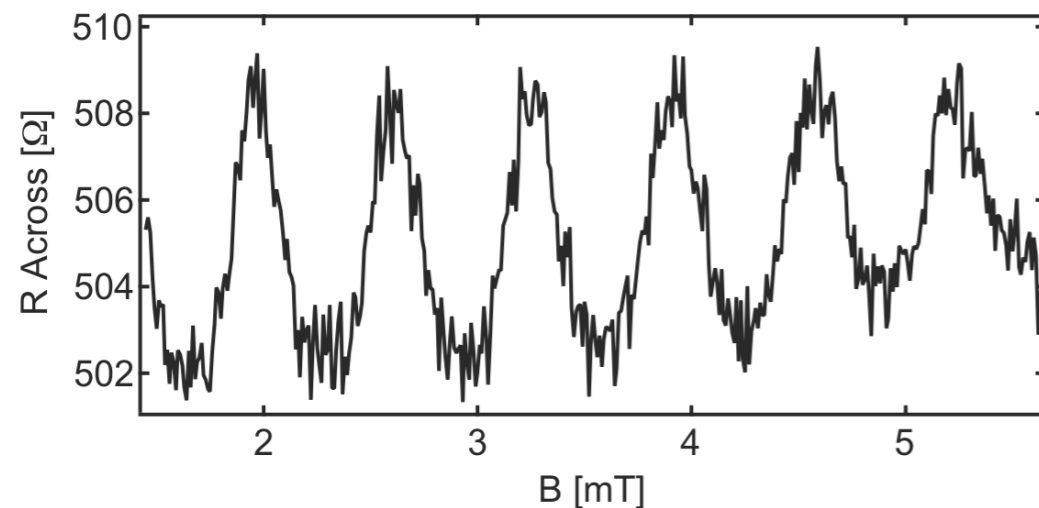
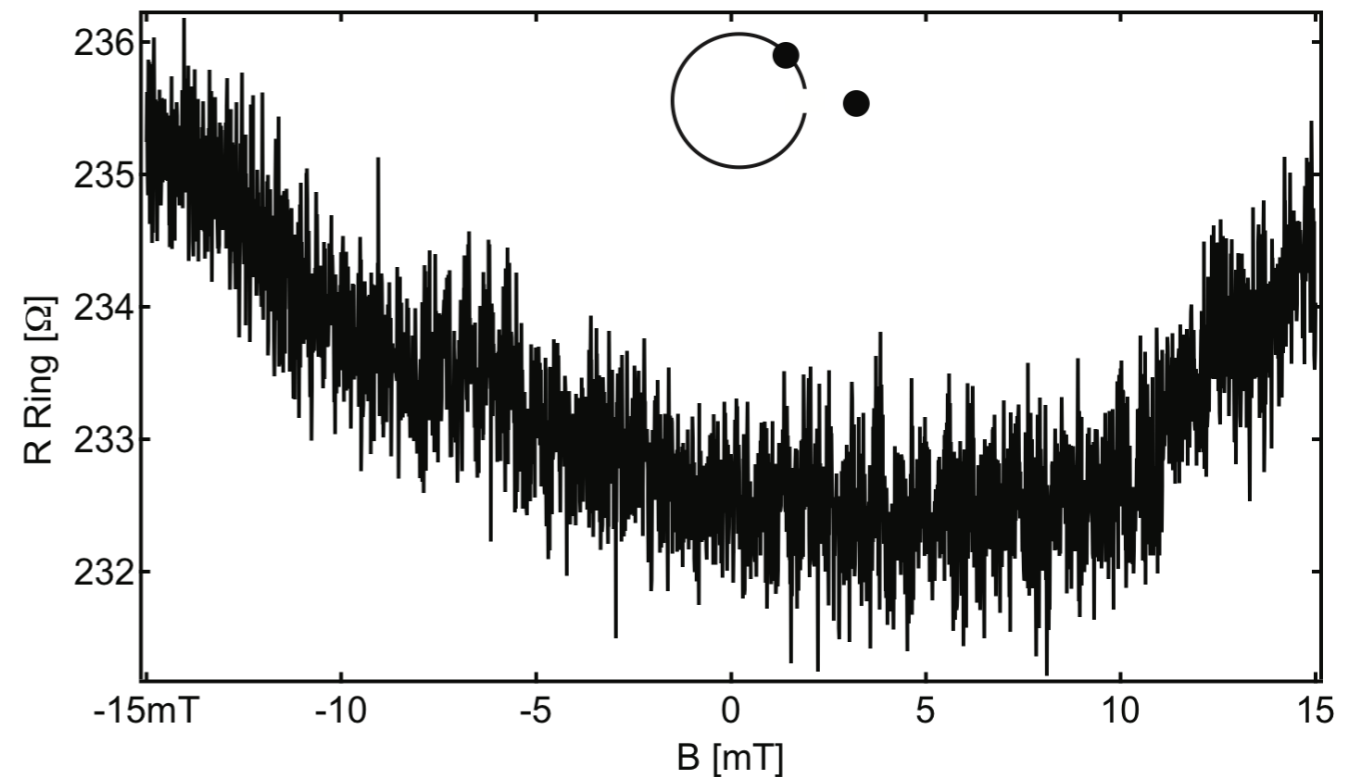
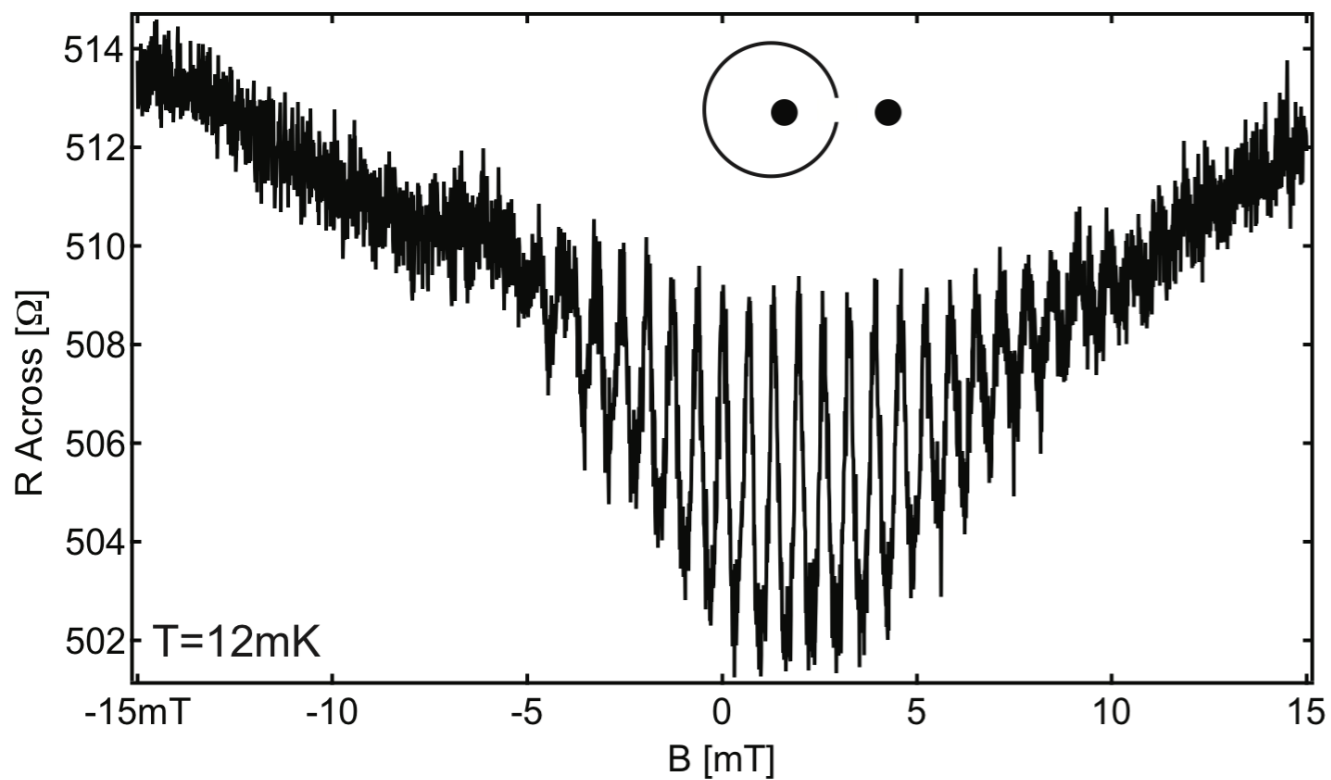
Creating the device

- Set the phase with magnetic field, measure resistance between source and drain, and between ring and drain



Measuring Transport Along Junctions

- At base, oscillations seen in the resistance across the junction



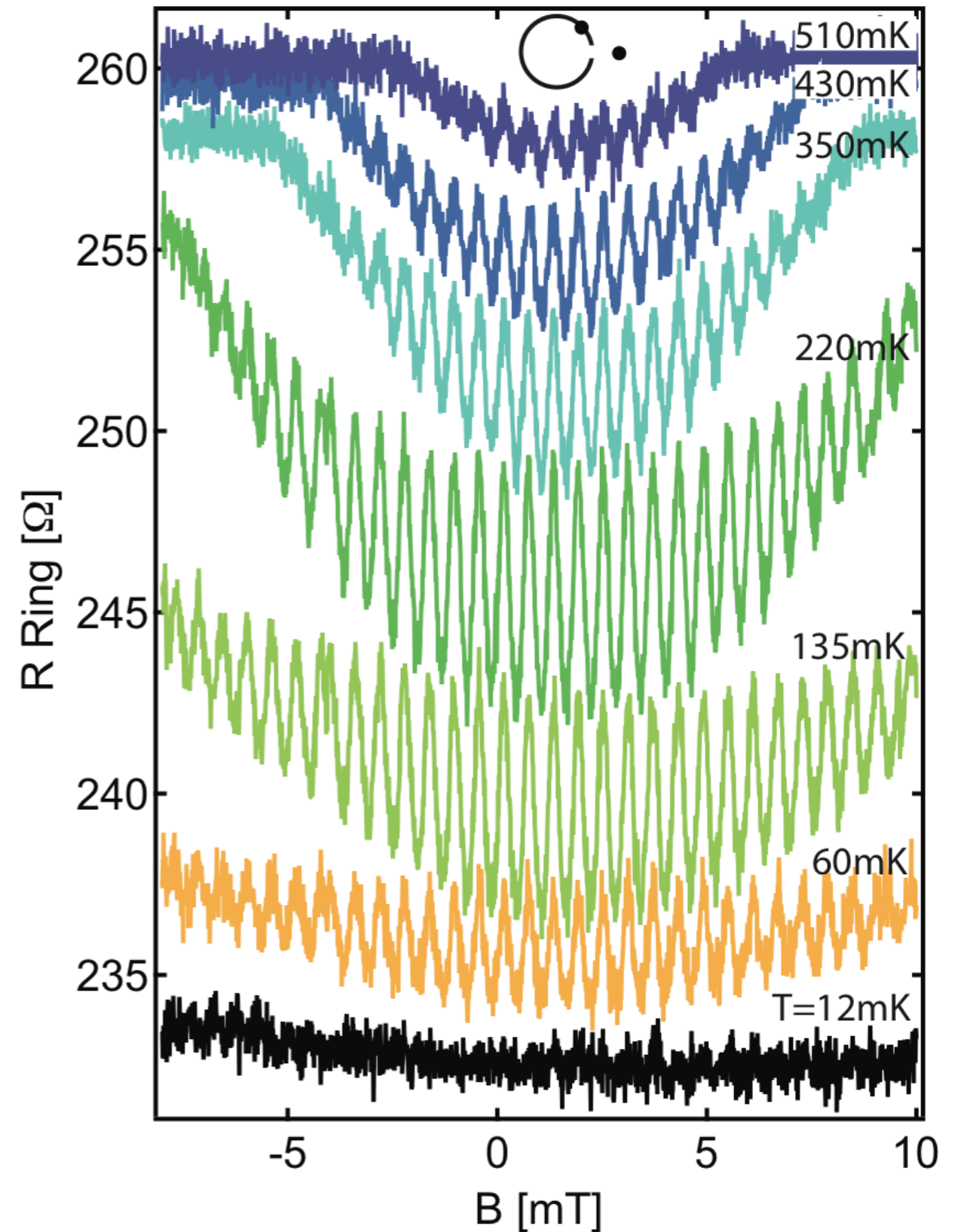
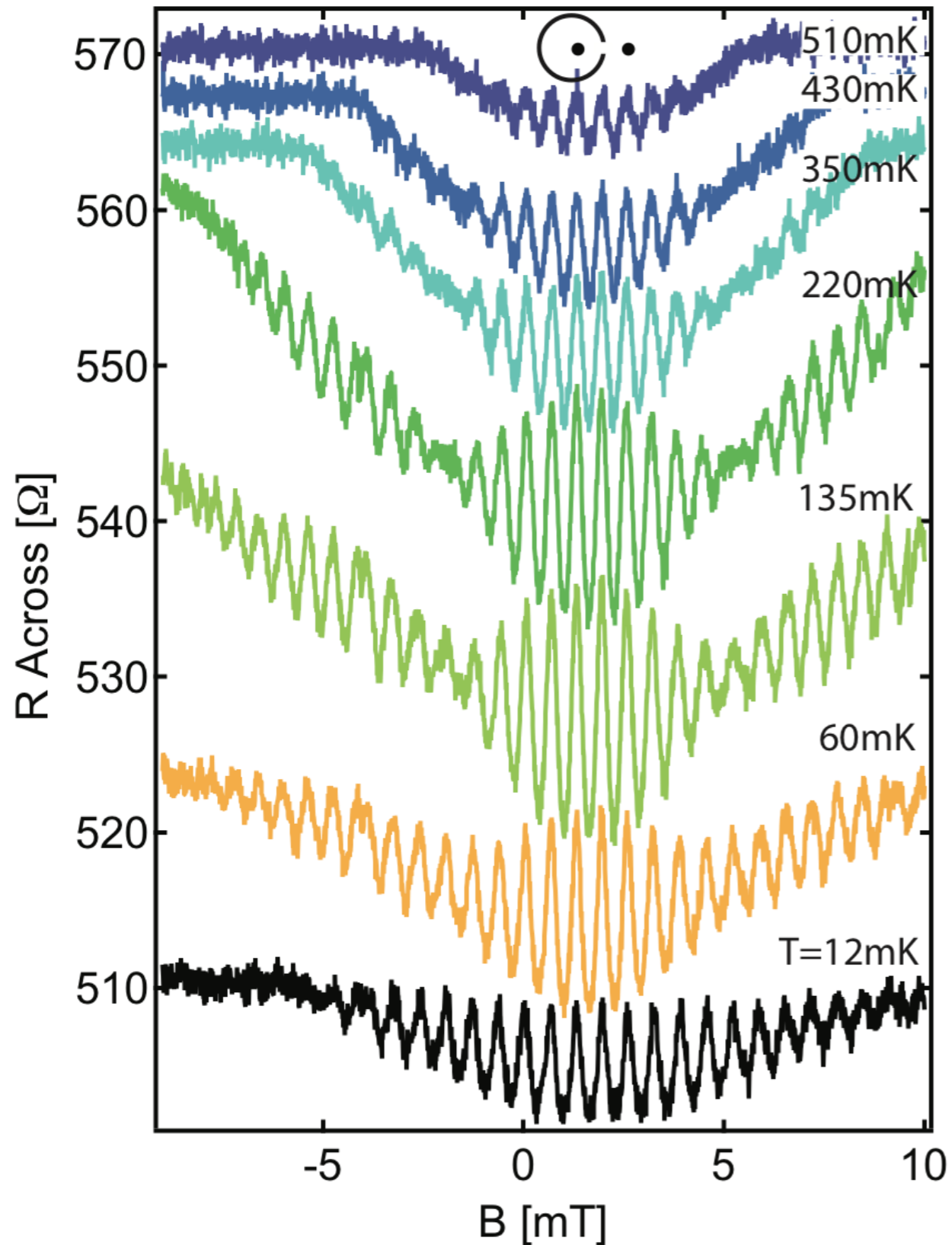
Ring inner radius of 0.8 microns and outer radius of 1.3 microns

Expected period for h/e is 2mT and for $h/2e$, 1mT (for inner radius)

Measured period is 0.6mT

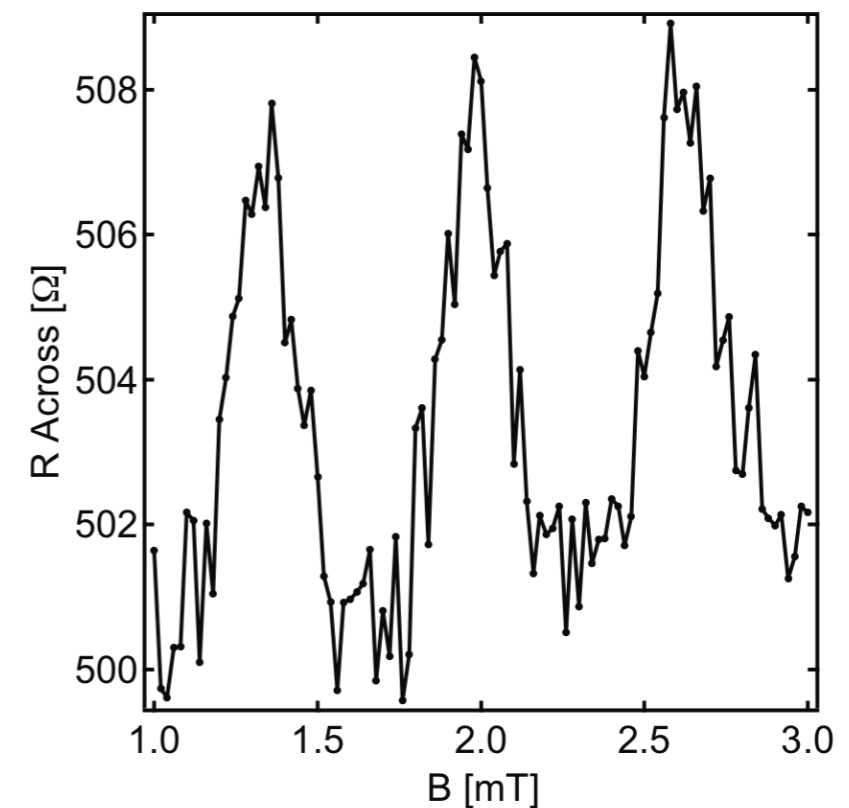
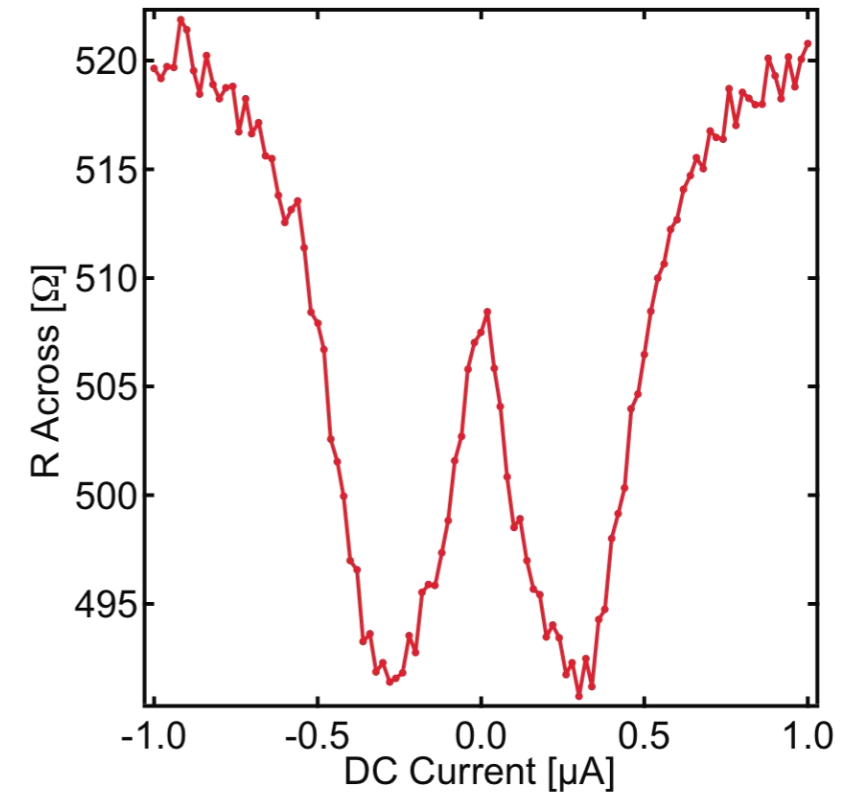
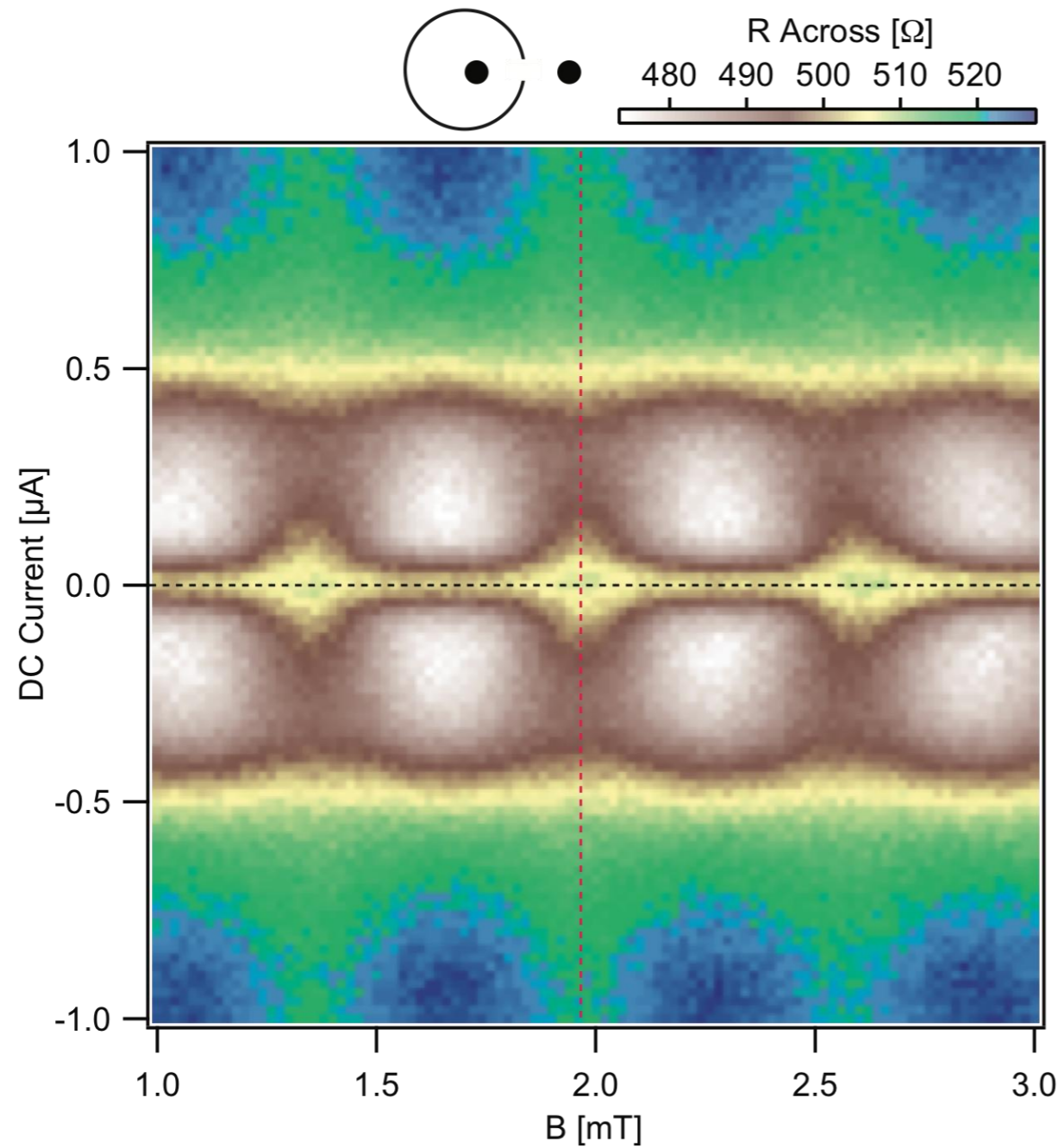
Temperature Dependence of Oscillations

- An unexpected, non-monotonic behavior observed



Bias Dependence of Resistance

- The minimum in resistance is not a zero applied bias



Summary

- Measured superconducting rings (with Bi_2Se_3 JJs) and dots. Rings showed the CPR is likely conventional. Dots shows we should look further into the effect of strong spin-orbit material on conventional superconductors
 - *What does this say about the S-strong-spin-orbit interface?*
- Made progress on transport in MBE TI films. Can now routinely tune through the Dirac point
 - *What can tuning get you in 3D TI Josephson junctions?*
- Measure conduction along phase controlled junctions and saw unexpected behavior in the temperature and bias-dependence of the measured resistance
 - *What are the prospects for measuring this effect and why would we observe this temperature dependence?*

Acknowledgements

- This work relies on a tremendous community of researchers.

Fab & measurement

Transport

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Tom Lippman
John Kirtley
Kathryn Moler

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Bulk Crystals

James Analytis
Andrew Bleich
Ian Fisher

Nanowires

Seung Sae Hong
Yi Cui

MBE

Xiaoyue He
Yongqin Li
Kehui Wu

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Jed Johnson
John Clarke
Mac Beasley
Xiaoliang Qi
Jens Bardarson
Joel Moore

